

High Step-up Ratio DC-DC Converter Topologies

Part II

Speaker: G. Spiazzi

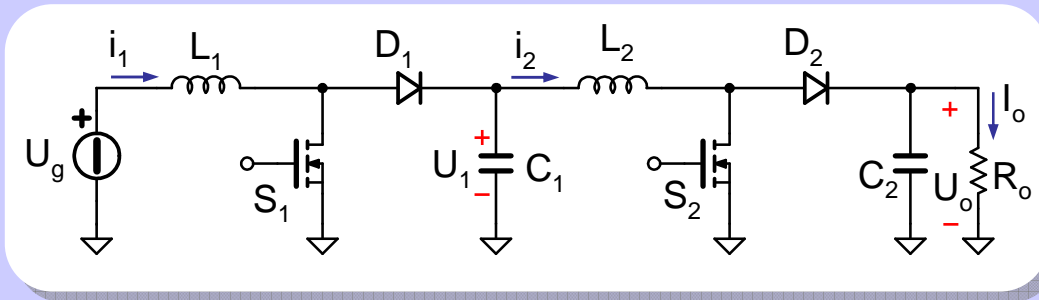
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L. Corradini

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Seminar Outline

- Why we need high step-up ratio converters?
 - Application fields
- Low power high step-up ratio topologies
 - Coupled inductors
- High power high step-up ratio topologies
 - Non isolated
 - Isolated

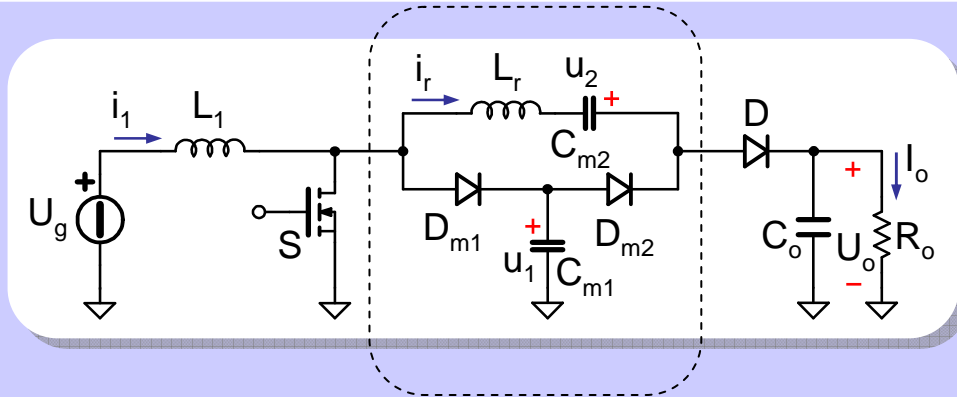
Cascaded Boost Converter



Voltage conversion ratio:
$$M = \frac{U_o}{U_g} = \frac{U_o}{U_1} \frac{U_1}{U_g} = \frac{1}{1-d_1} \frac{1}{1-d_2}$$

- ↑ Reduced S_1 and D_1 voltage stress
- ↑ High flexibility
- ↑ Suitable for high power applications through interleaving connections
- ↓ Total power processed twice
- ↓ High S_2 and D_2 voltage stress

Boost with Voltage Multiplier Cells



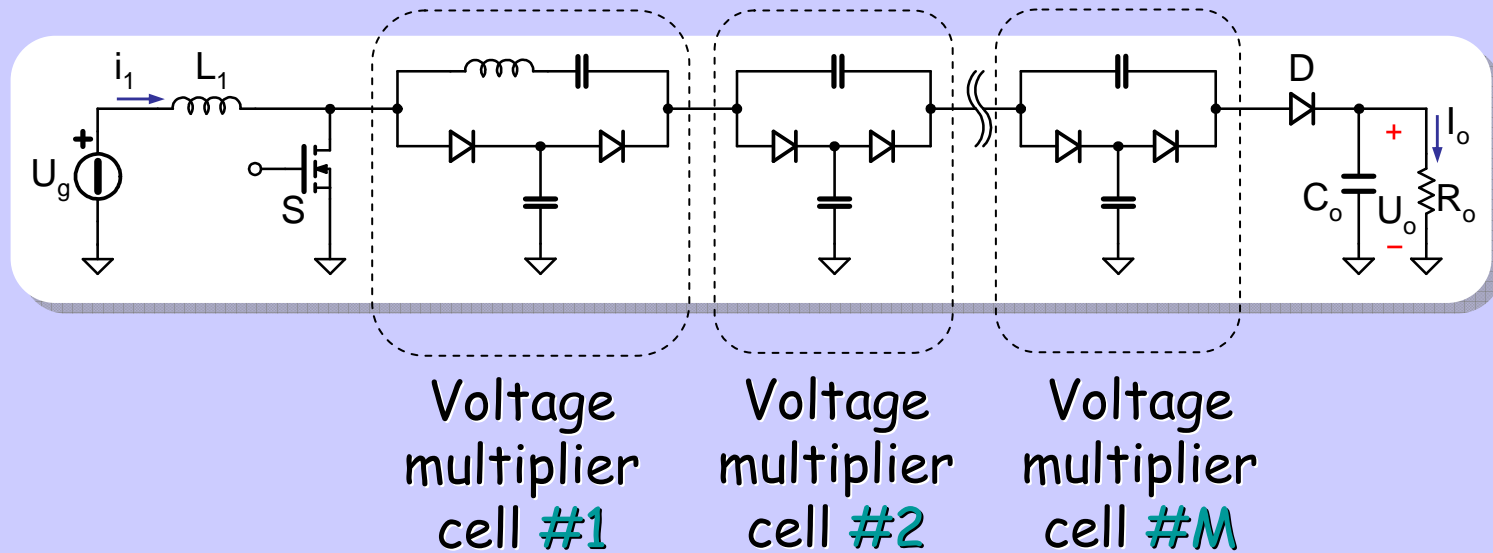
Voltage multiplier cell

Voltage conversion ratio:

$$M = \frac{U_o}{U_g} \approx \frac{2}{1-d}$$

- ↑ Reduced switch and diode voltage stress ($U_{DS} \approx U_o/2$)
- ↑ ZCS and soft diode turn off through the use of a resonant inductor L_r
- ↑ Suitable for high power applications through interleaving connections
- ↓ Maximum and minimum duty-cycle limitation to guarantee soft commutations
- ↓ High switch RMS current
- ↓ Voltage stress reduction related to the number of cells

Boost with Voltage Multiplier Cells



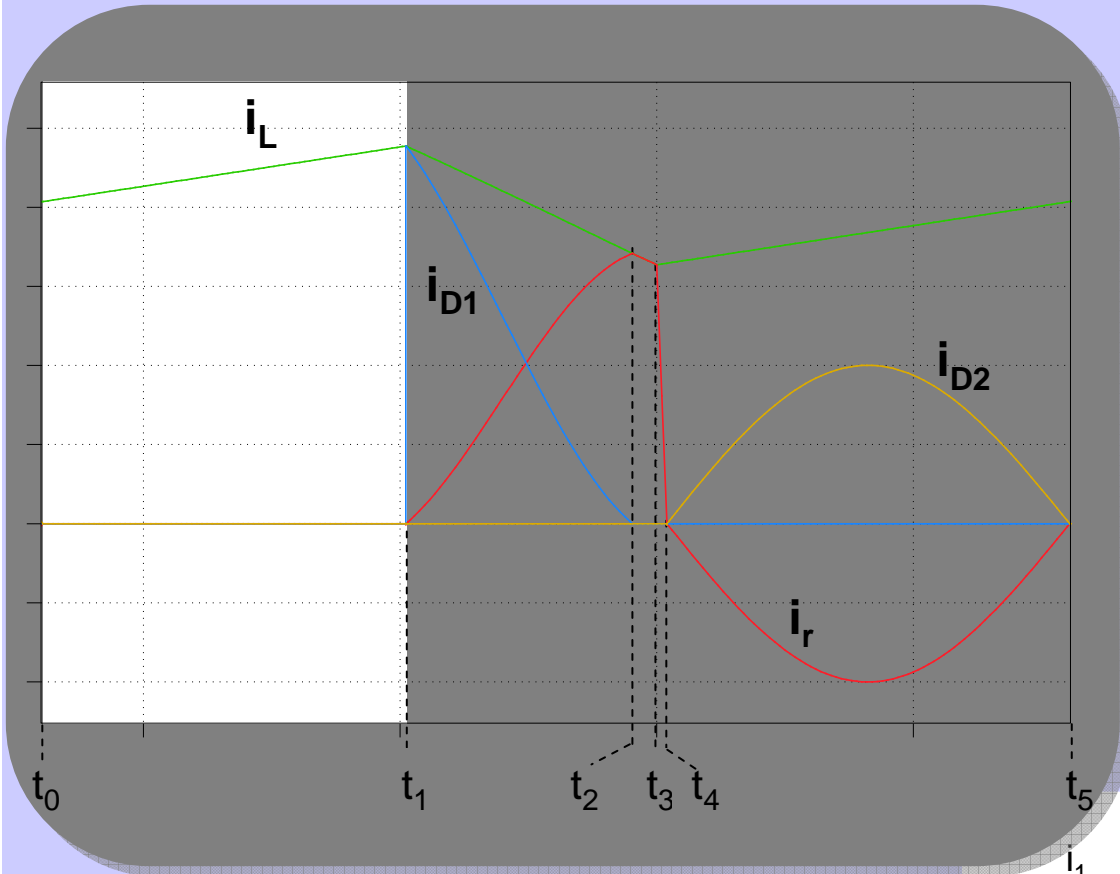
Voltage conversion ratio:

$$M = \frac{U_o}{U_g} \approx \frac{M+1}{1-d}$$

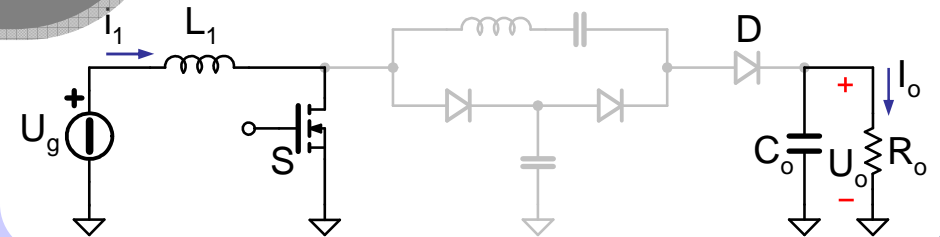
Switch voltage stress:

$$U_{DS} \approx \frac{U_o}{M+1}$$

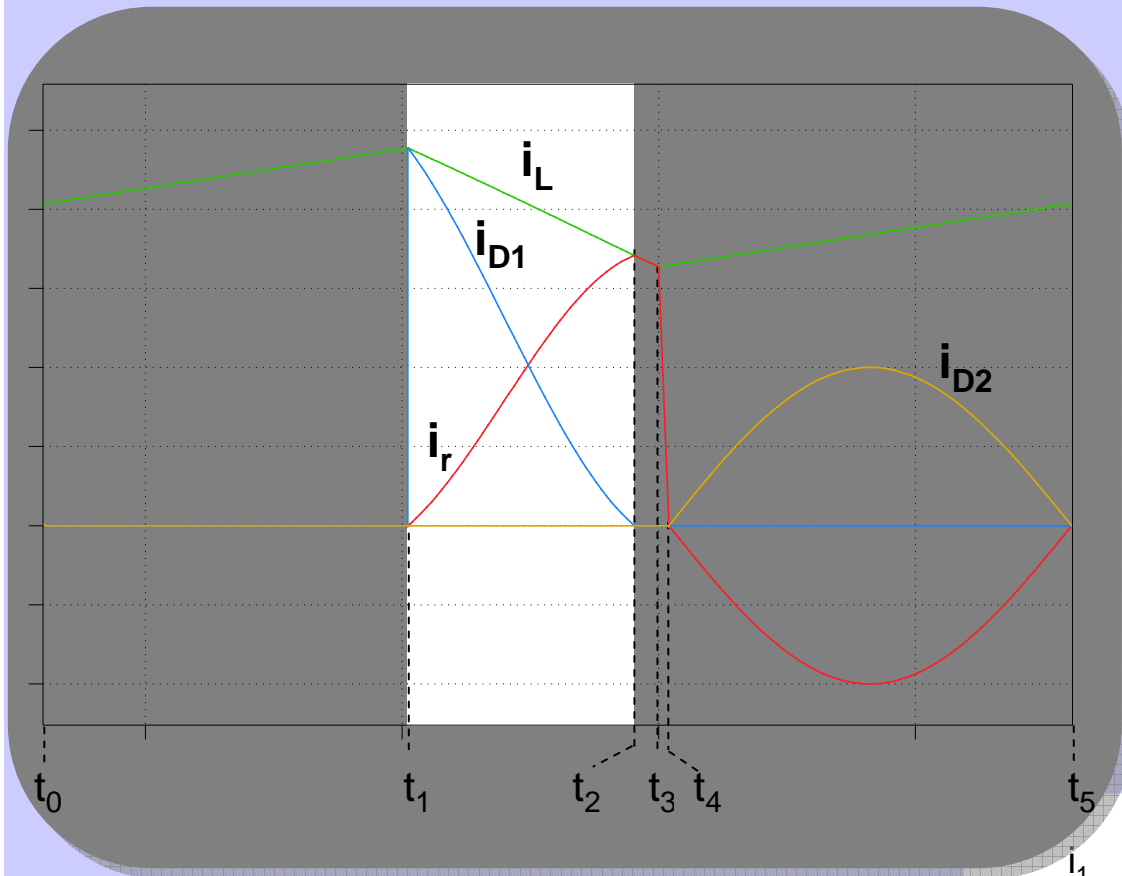
Converter Operation (CCM)



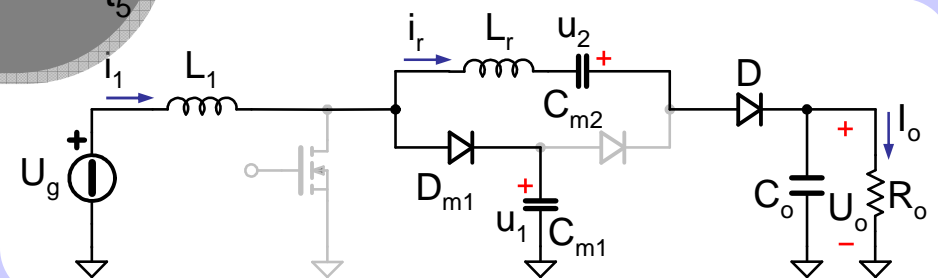
$$T_{01} = t_1 - t_0$$



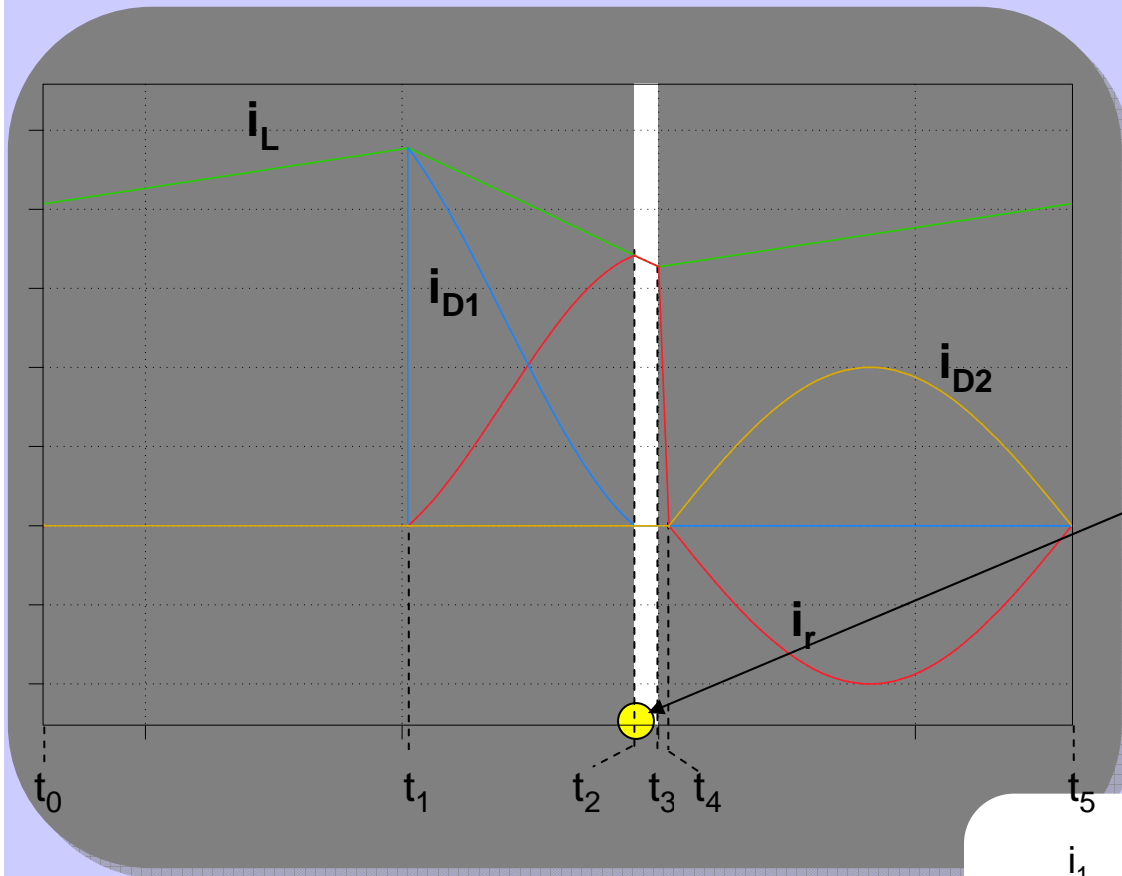
Converter Operation (CCM)



$$T_{12} = t_2 - t_1$$

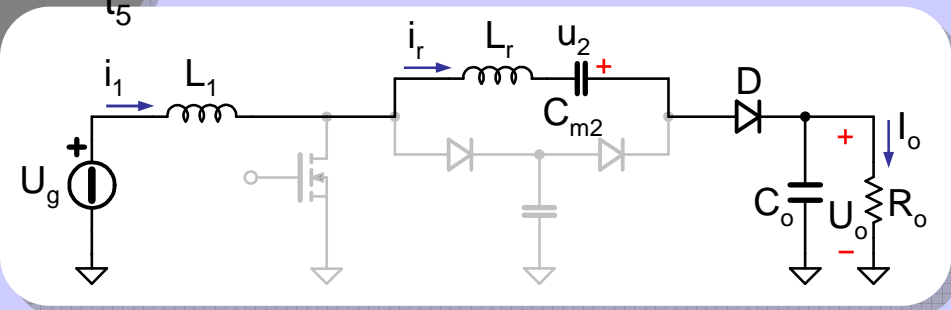


Converter Operation (CCM)

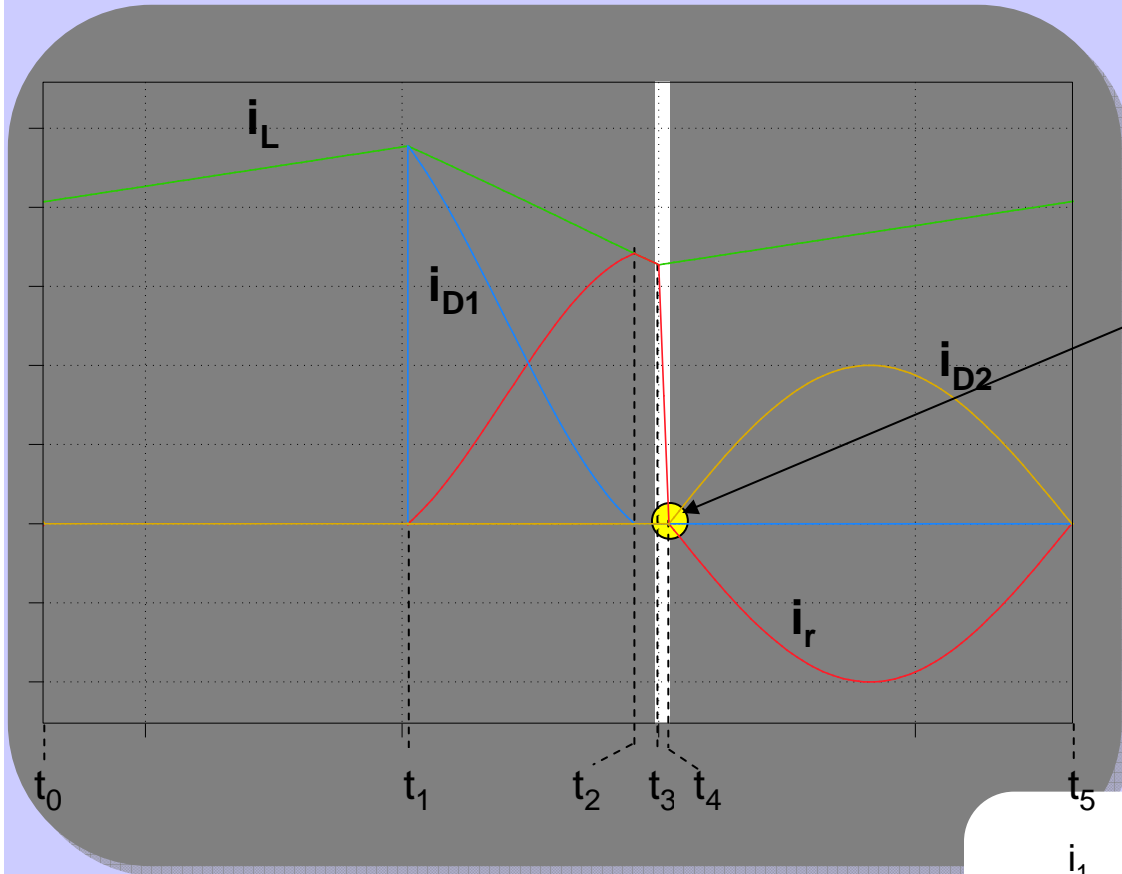


Soft D_{m1} turn off

$$T_{23} = t_3 - t_2$$

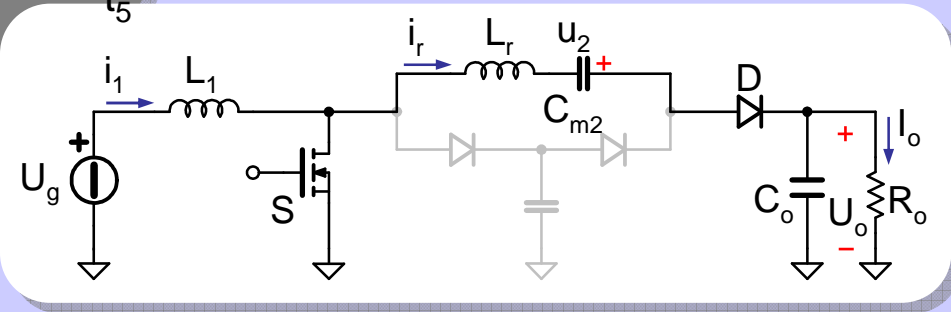


Converter Operation (CCM)

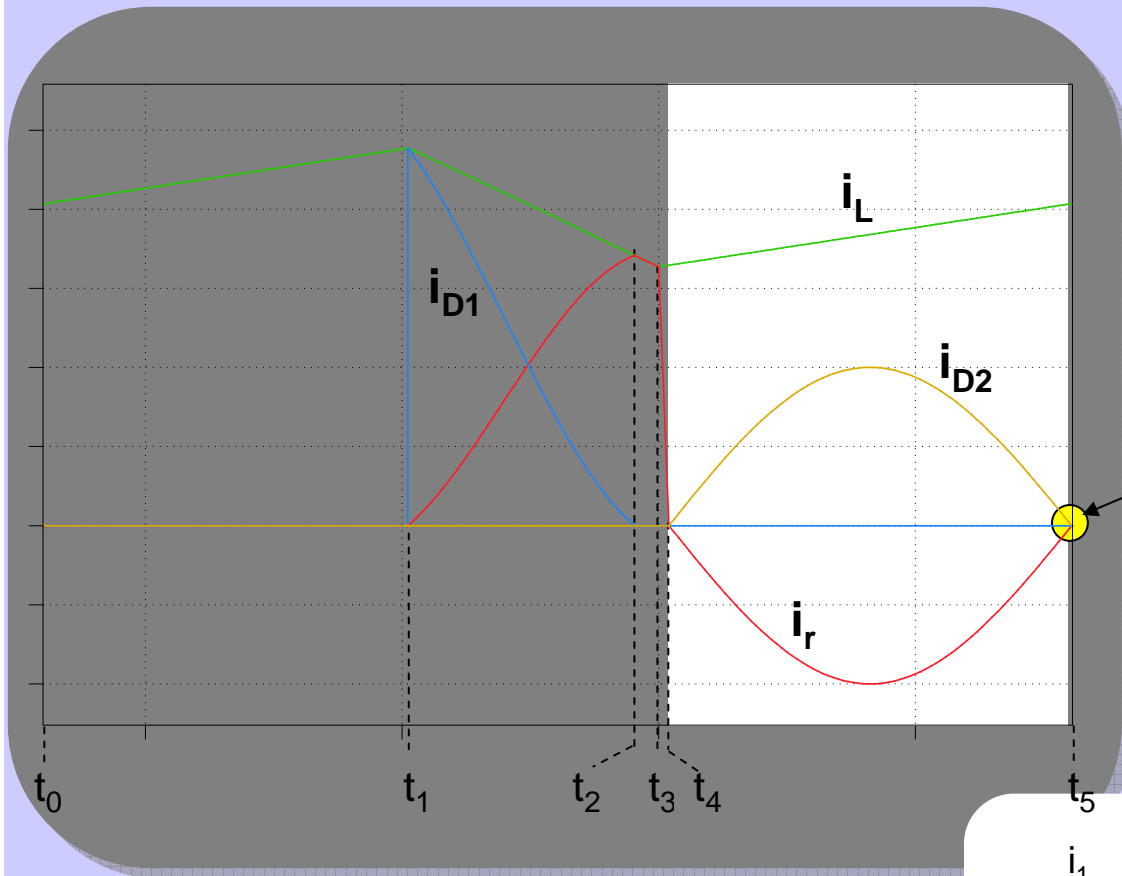


Soft D turn off

$$T_{34} = t_4 - t_3$$

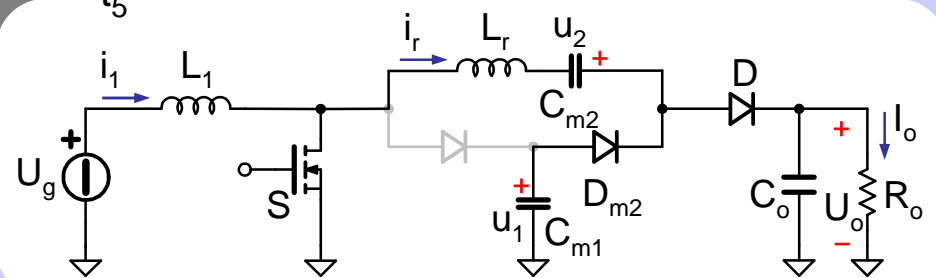


Converter Operation (CCM)

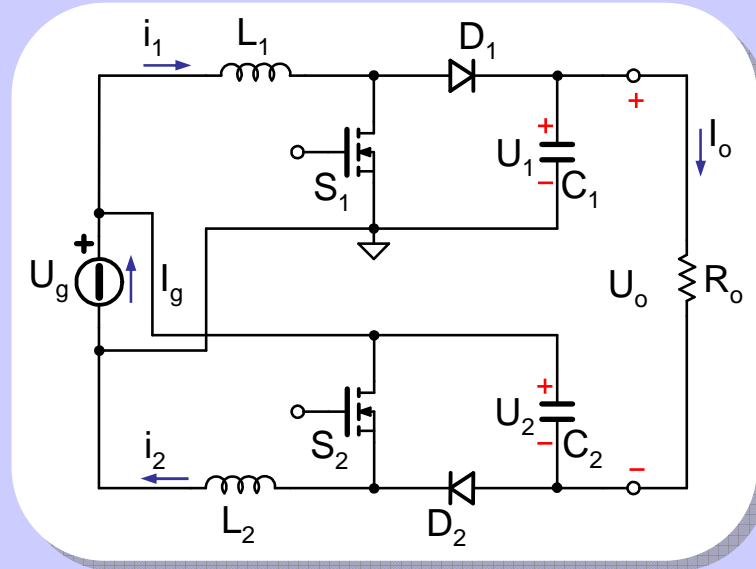


Soft D_{m2} turn off

$$T_{45} = t_5 - t_4$$



Dual Boost Converter



Voltage conversion ratio:

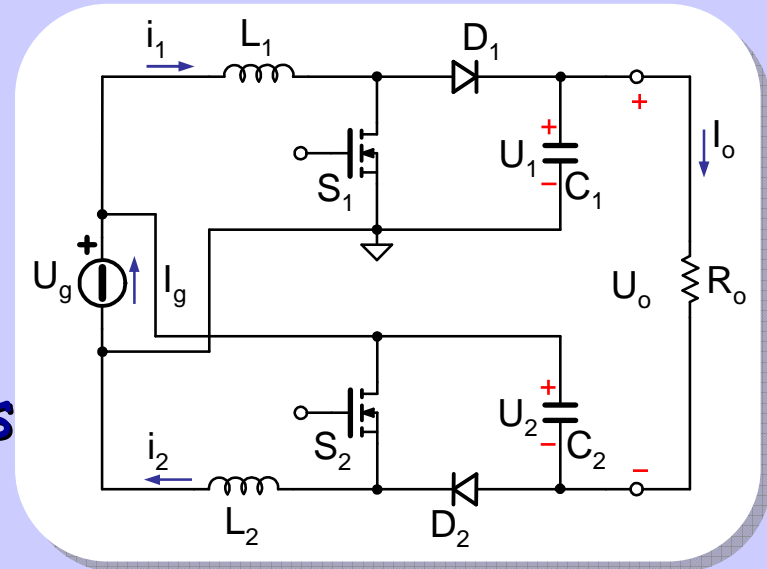
$$M = \frac{U_o}{U_g} = \frac{1+d}{1-d}$$

Output voltage of each converter:

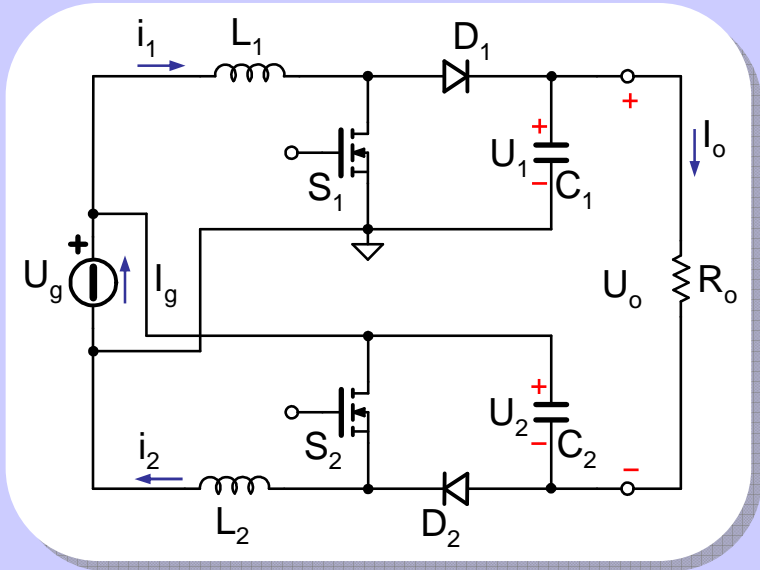
$$M_1 = \frac{U_1}{U_g} = M_2 = \frac{U_2}{U_g} = \frac{1}{1-d}$$

Dual Boost Converter

- ↑ Reduced switch and diode voltage stresses
- ↑ Inductor L_1 and L_2 rated roughly at half of total input current
- ↑ Suitable for high power applications through interleaving connections of each module
- ↓ Need for isolated gate driver
- ↓ Floating load connection
- ↓ Limited switch voltage stress reduction
- ↓ Penalty in the converter efficiency (negligible for high conversion ratios)



Dual Boost Converter



Power processed by each module:

$$P_1 = U_1 I_o = P_2 = U_2 I_o = P$$

Efficiency of each module:

$$\eta_1 = \frac{P_1}{P_g} = \frac{P_1}{P_1 + P_d}$$

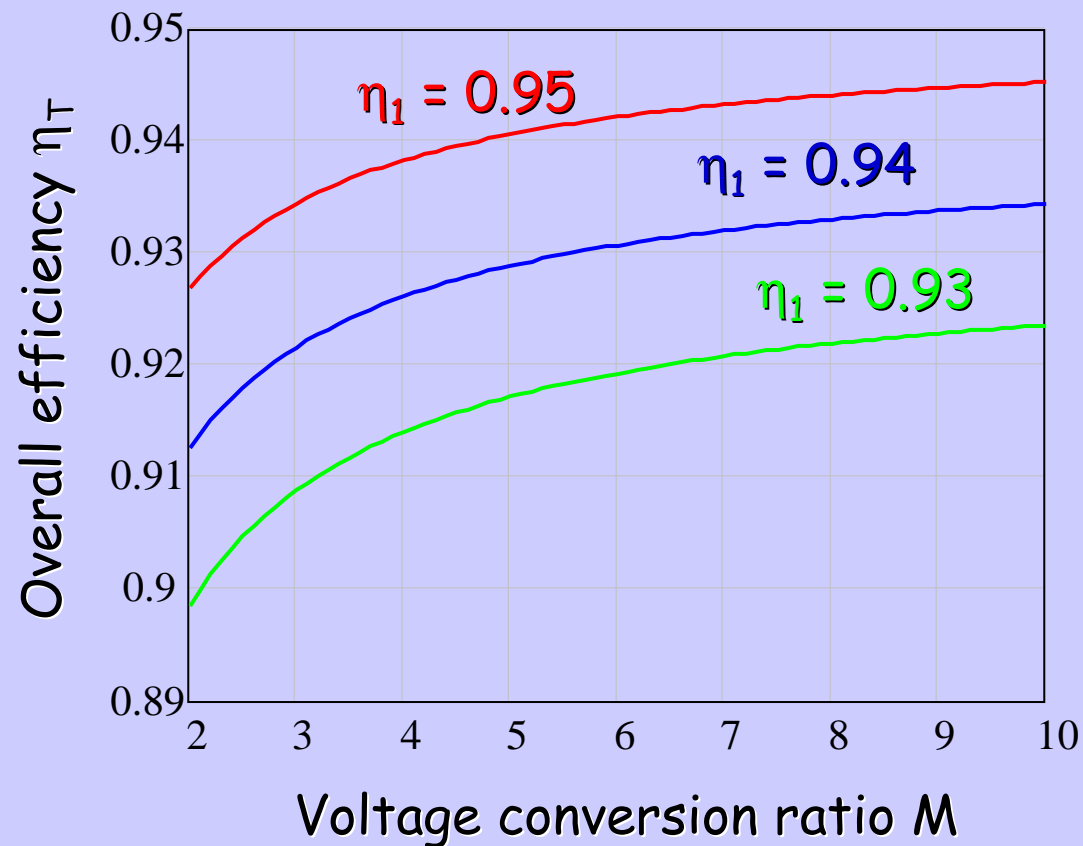
Efficiency reduction:

$$\eta_T = \frac{P_o}{P_g} = \frac{P_o}{P_o + 2P_d} = \frac{(U_1 + U_2 - U_g)I_o}{(U_1 + U_2 - U_g)I_o + 2P_d} = \frac{2P - U_g I_o}{2(P + P_d) - U_g I_o}$$

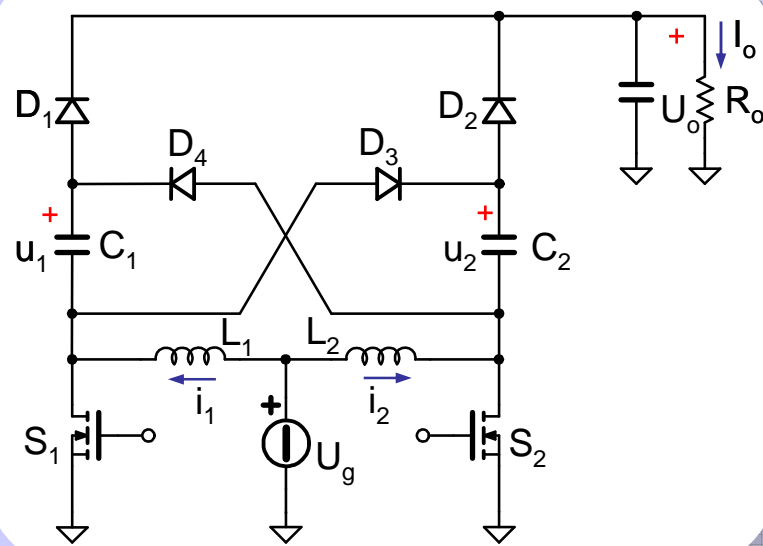
$$\eta_T = \frac{1 - \frac{1}{2M_1}}{\frac{1}{\eta_1} - \frac{1}{2M_1}} = \frac{2M_1 - 1}{\frac{2M_1}{\eta_1} - 1} = \frac{M}{\frac{M+1}{\eta_1} - 1} = \frac{\eta_1 M}{M+1 - \eta_1}$$

Dual Boost Converter

Efficiency reduction: $\eta_T = \frac{\eta_1 M}{M + 1 - \eta_1}$



Interleaved Boost with Voltage Multiplier



$$U_1 = U_2 = \frac{U_o}{2}$$

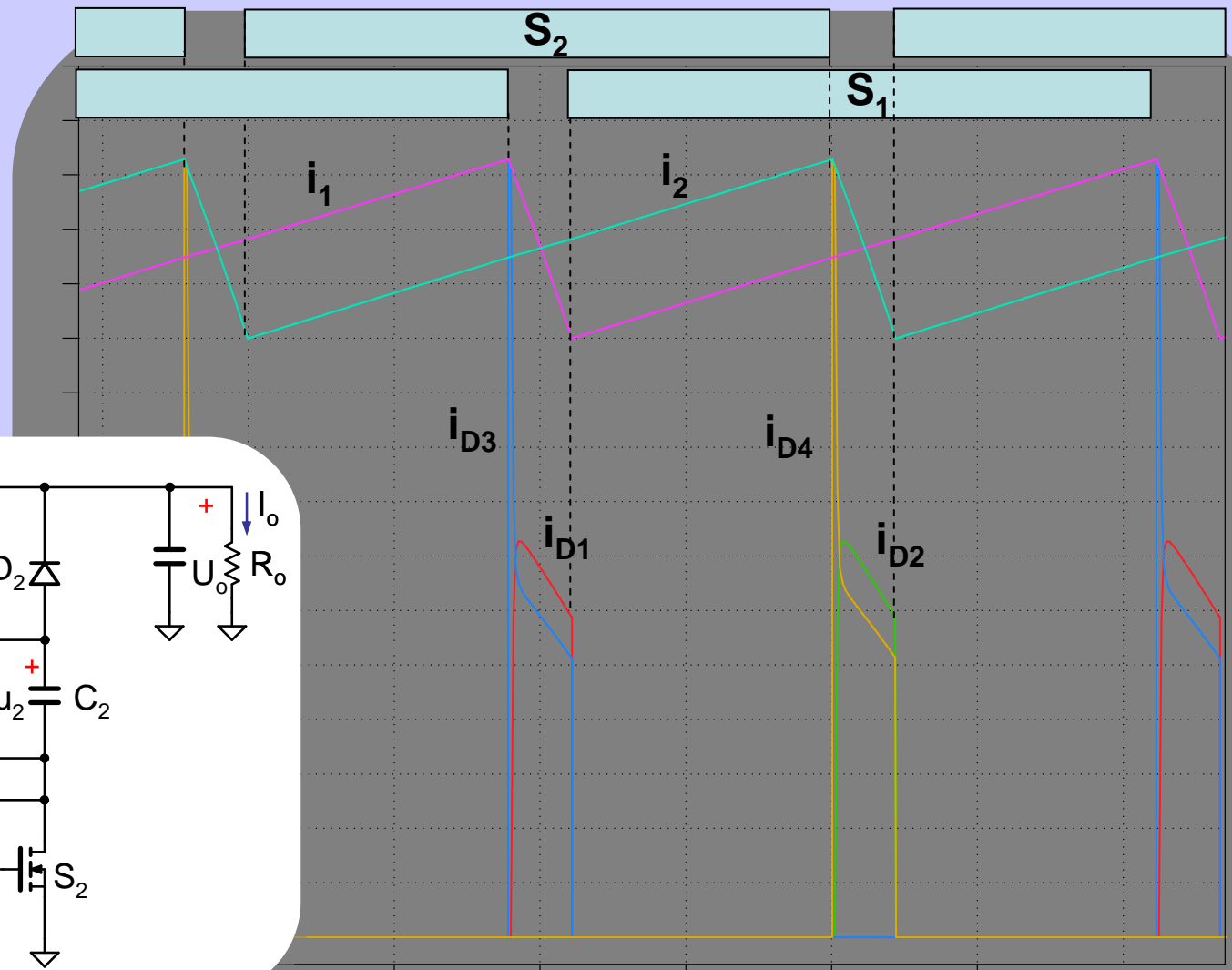
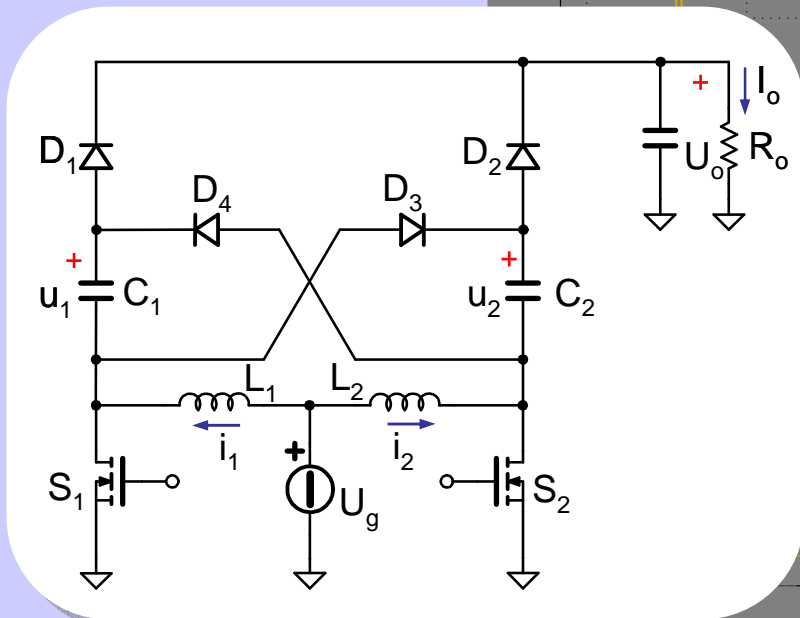
Voltage conversion
ratio $d > 0.5$:

$$M = \frac{U_o}{U_g} = \frac{2}{1-d}$$

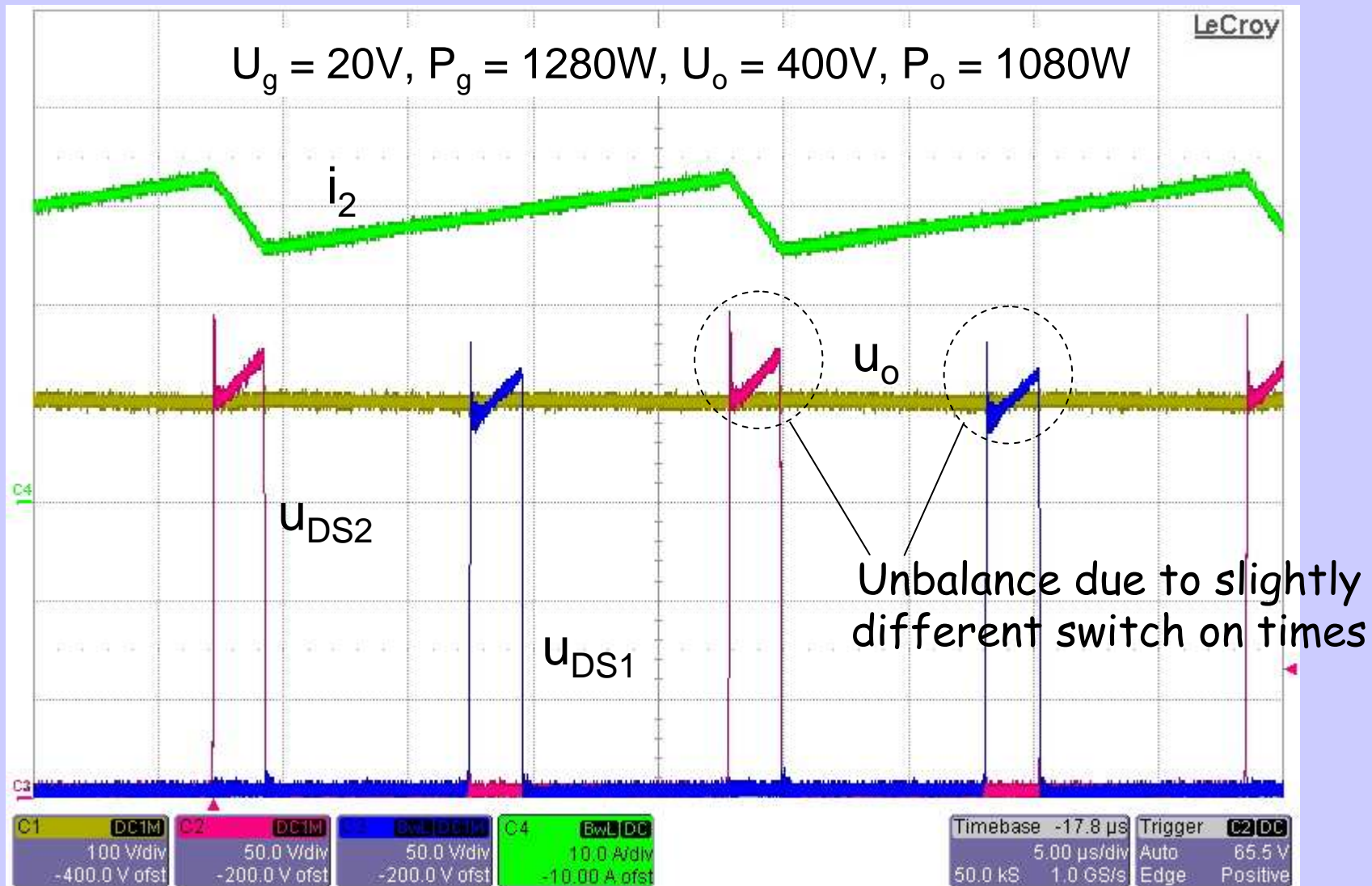
- ↑ Reduced switch and diode voltage stress ($U_o/2$)
- ↑ Inductor L_1 and L_2 rated at half of total input current
- ↑ Reduced input current ripple due to interleaved operation
- ↓ Voltage multiplier cell operation requires $d > d_{\min}$
- ↓ More ringing on switch voltage due to capacitor ESL

Current Waveforms $d > 0.5$

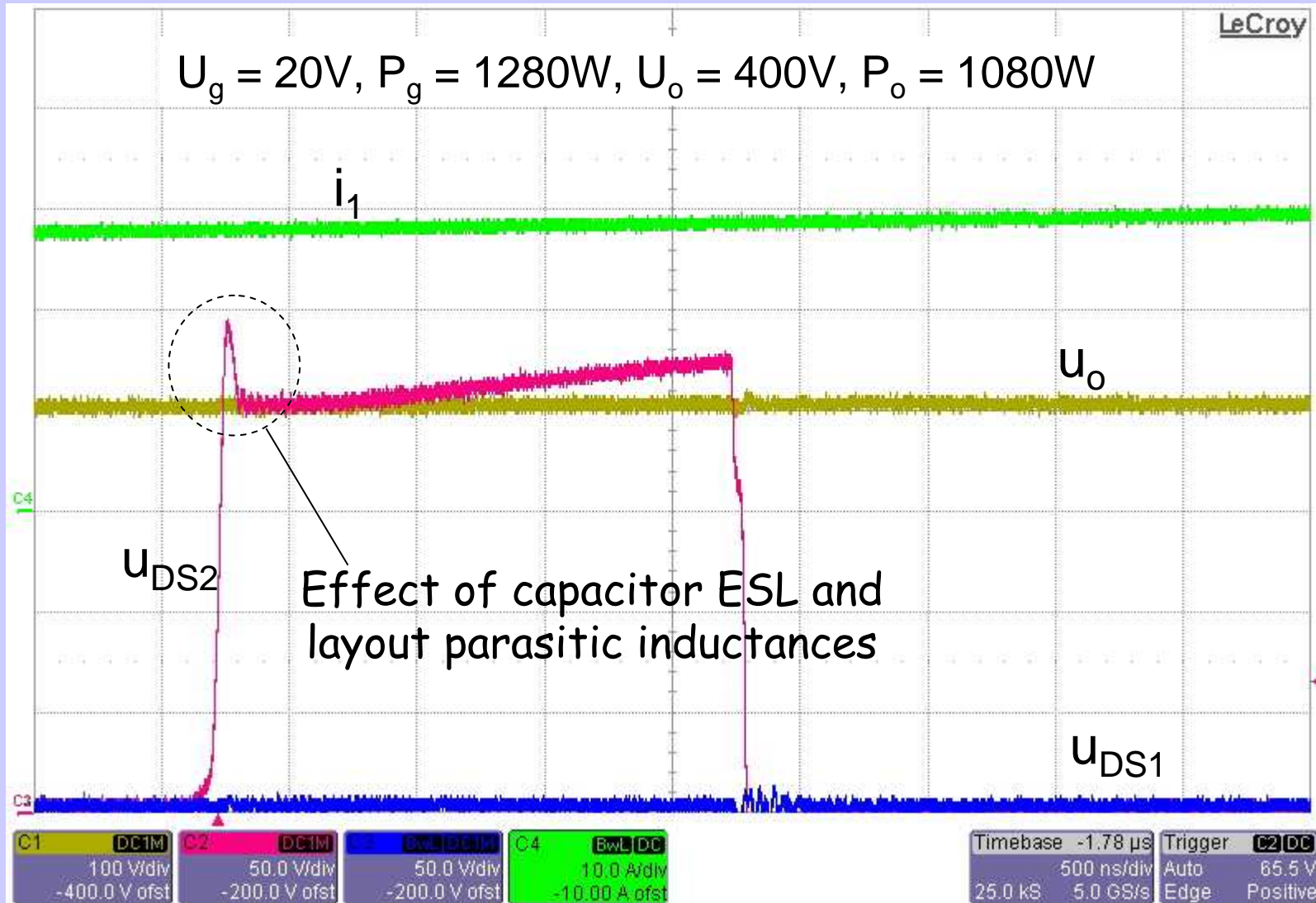
$$U_1 = U_2 = \frac{U_o}{2}$$



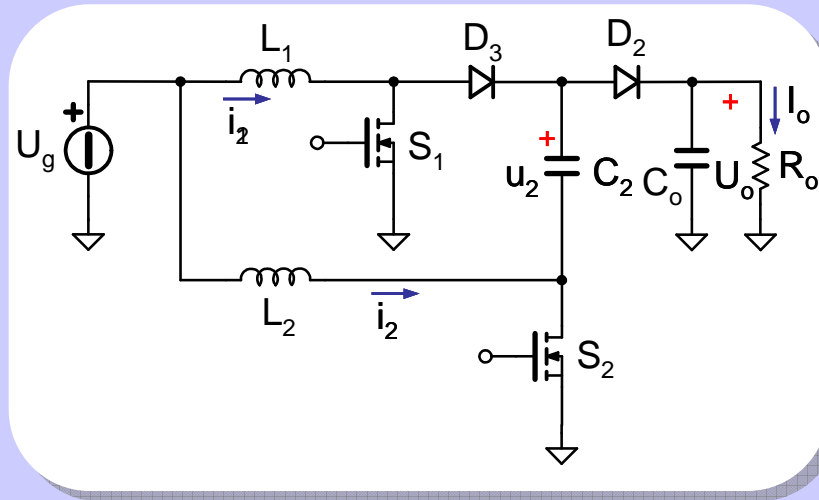
Interleaved Boost with Voltage Multiplier



Interleaved Boost with Voltage Multiplier



Boost with Voltage Doubler



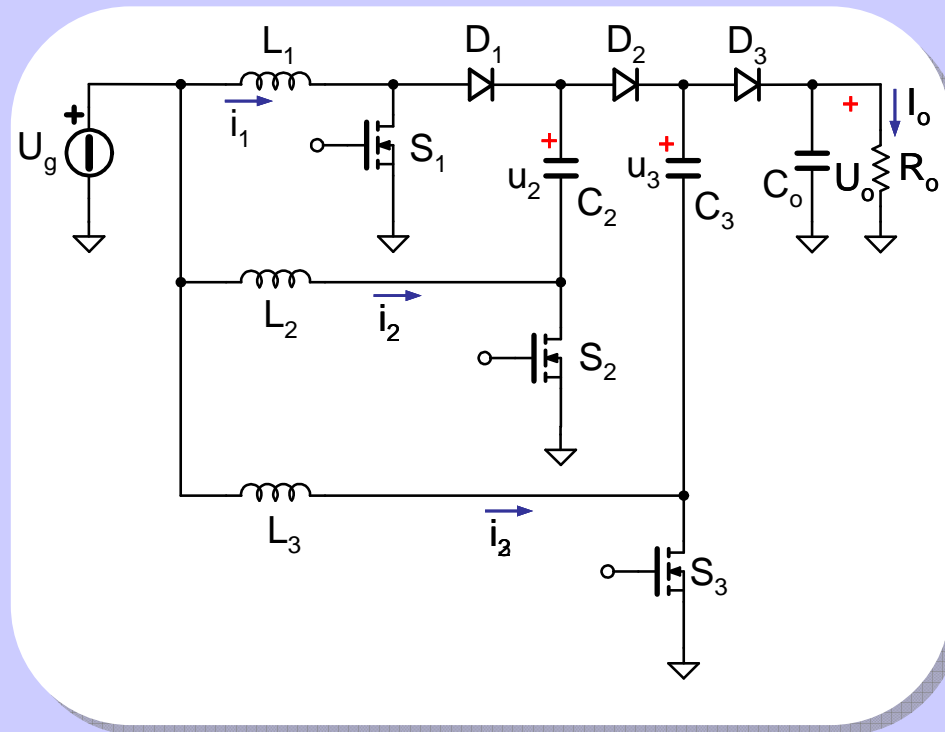
$$U_2 = \frac{U_o}{2}$$

Voltage conversion ratio $d > 0.5$: $M = \frac{U_o}{U_g} = \frac{2}{1-d}$

Similar behavior as the interleaved boost with voltage multiplier

Problem: for $d < 0.5$ the switch voltage stress (S_1) becomes the output voltage

Extension to Higher Step-up Ratios

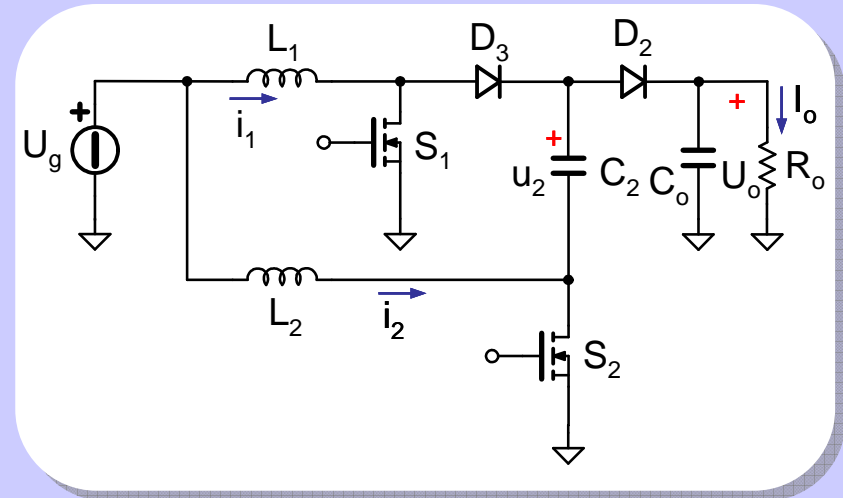
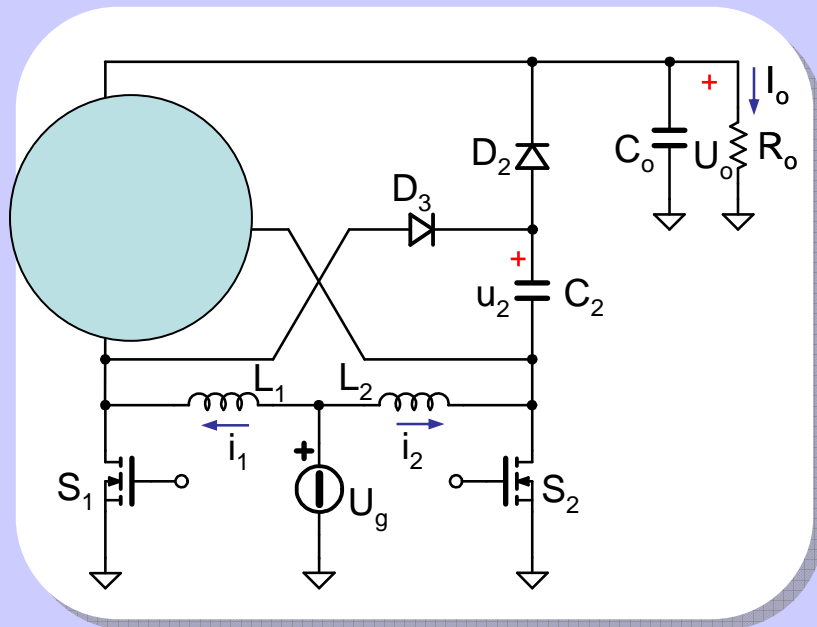


$$U_2 = \frac{U_3}{2} = \frac{U_o}{3}$$

Voltage conversion ratio $d > 2/3$: $M = \frac{U_o}{U_g} = \frac{3}{1-d}$

Boost with Voltage Doubler

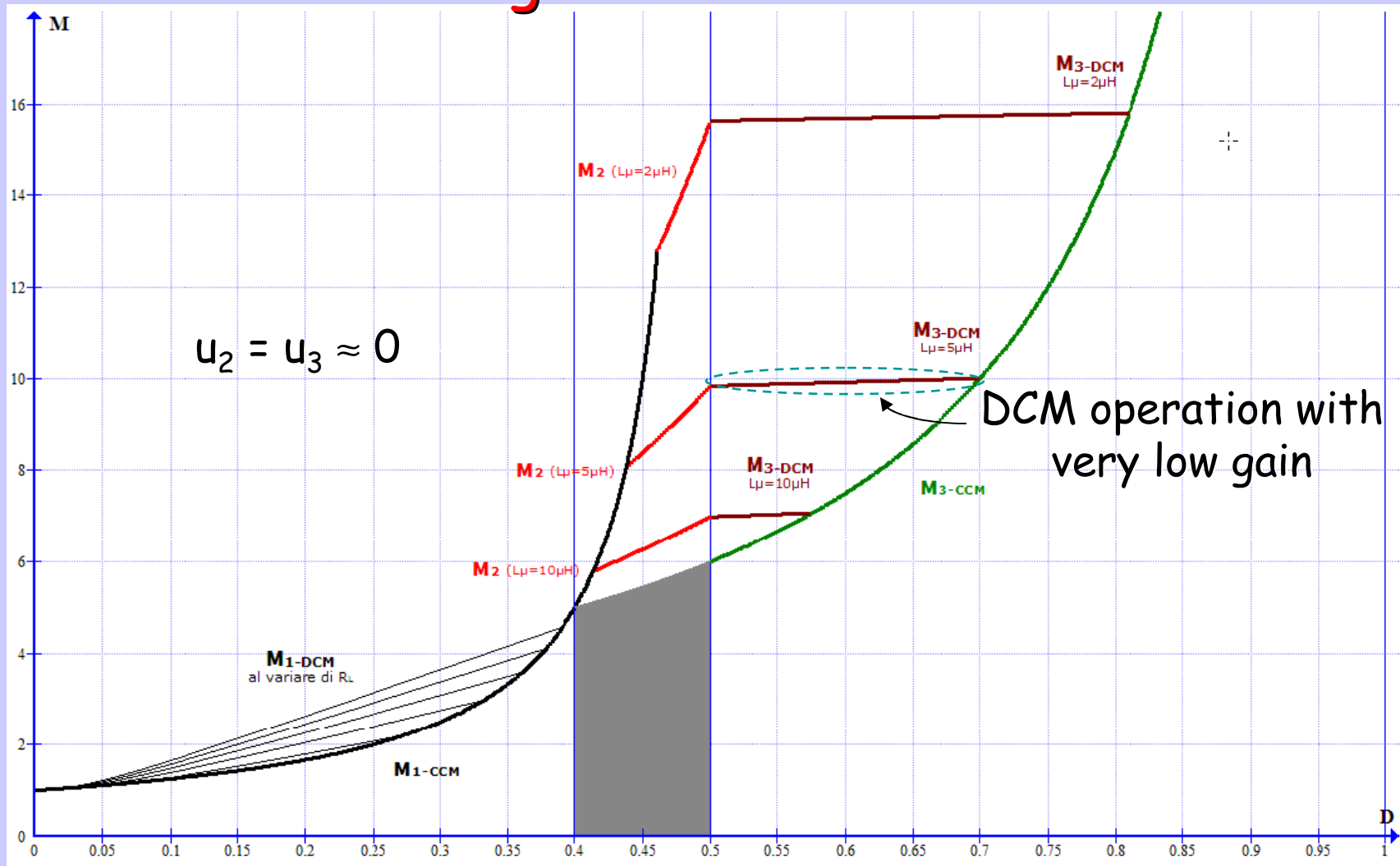
Interleaved boost with voltage multiplier
versus Boost with voltage doubler



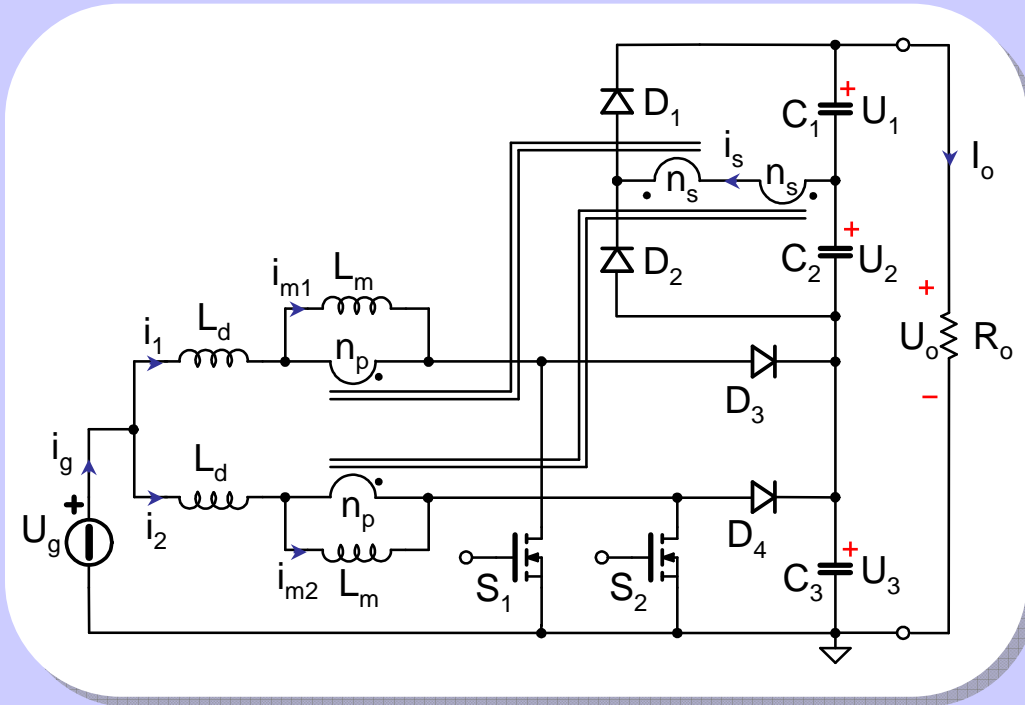
Similar behavior for duty-cycle higher than 50% but the structure becomes **asymmetric**

Boost with Three-state Switching Cell

Voltage conversion ratio



Interleaved Boost with Coupled Inductors and Voltage Multiplier



Voltage conversion ratio $d > d_{min}$ (CCM):

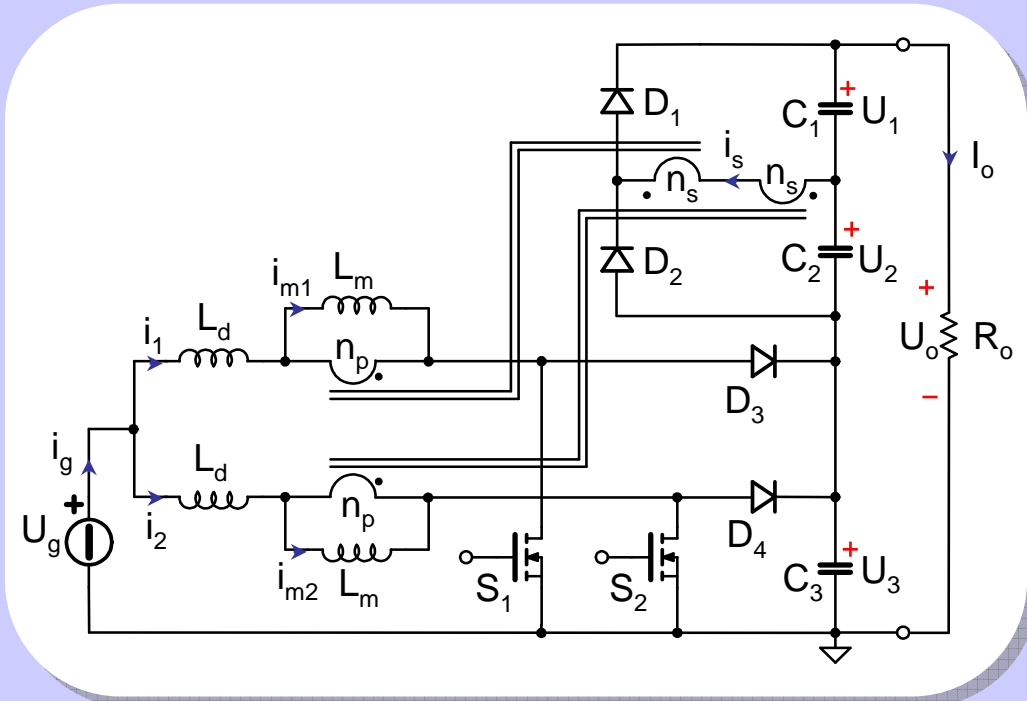
$$M = \frac{U_o}{U_g} \approx \left(\frac{n+2}{n} \right) \frac{1}{1-d}$$

$$n = \frac{N_p}{N_s} \quad \frac{L_m}{L_m + L_d} \approx 1$$

Normalized switch voltage stress:

$$U_{swN} = \frac{U_{sw}}{U_o} = \frac{U_3}{U_o} \approx \frac{n}{n+2}$$

Interleaved Boost with Coupled Inductors and Voltage Multiplier



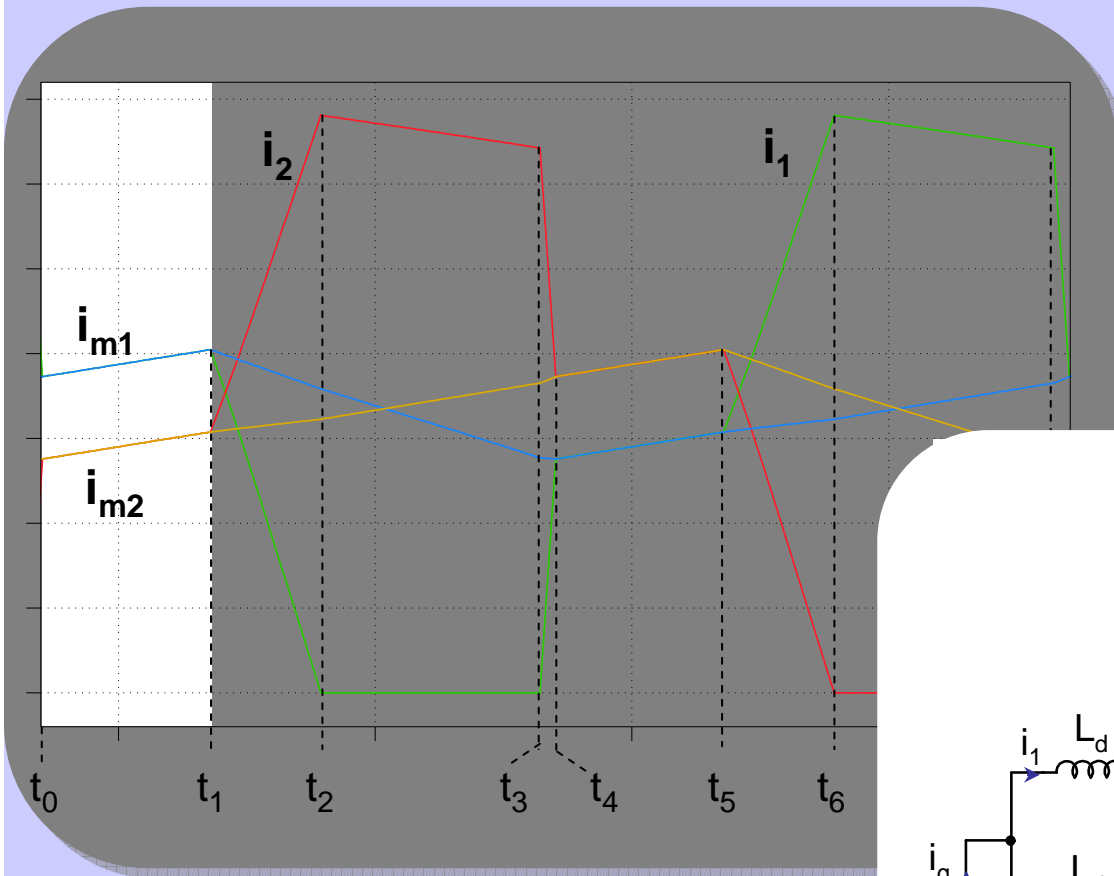
Voltage conversion ratio $d > d_{min}$ (CCM):

$$M = \frac{U_o}{U_g} \approx \left(\frac{n+2}{n} \right) \frac{1}{1-d}$$

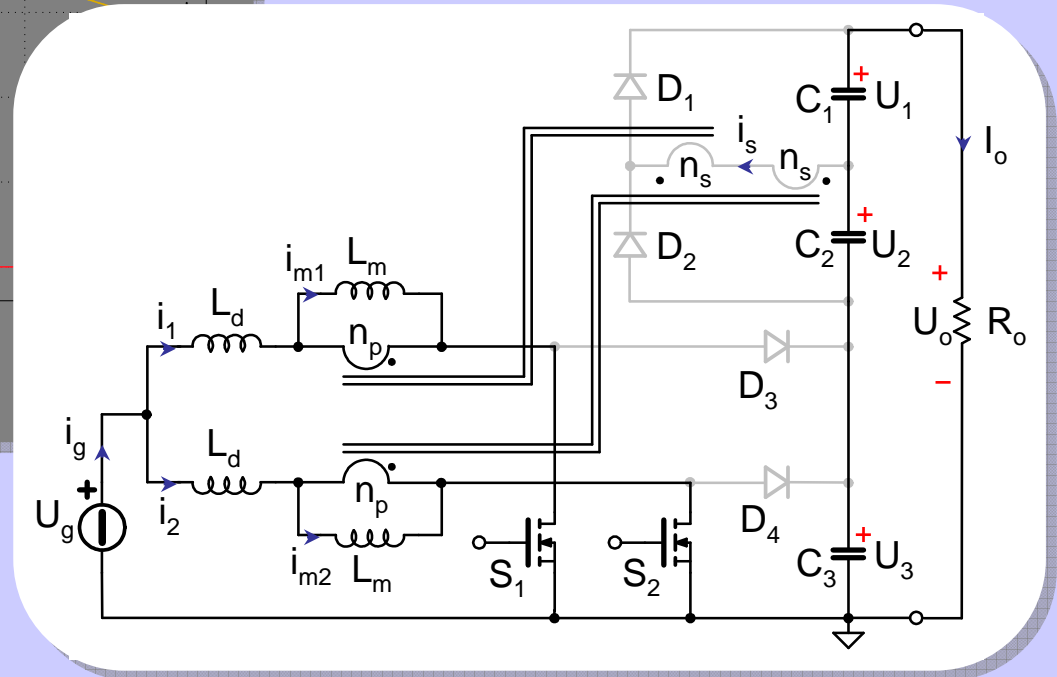
$$n = \frac{N_p}{N_s} \quad \frac{L_m}{L_m + L_d} \approx 1$$

- ↑ Reduced switch and diode voltage stress (depending on n)
- ↑ Reduced input current ripple due to interleaved operation
- ↑ No reverse recovery losses (ZCS turn on)
- ↓ Voltage multiplier cell operation requires $d > d_{min}$
- ↓ High switch current stress

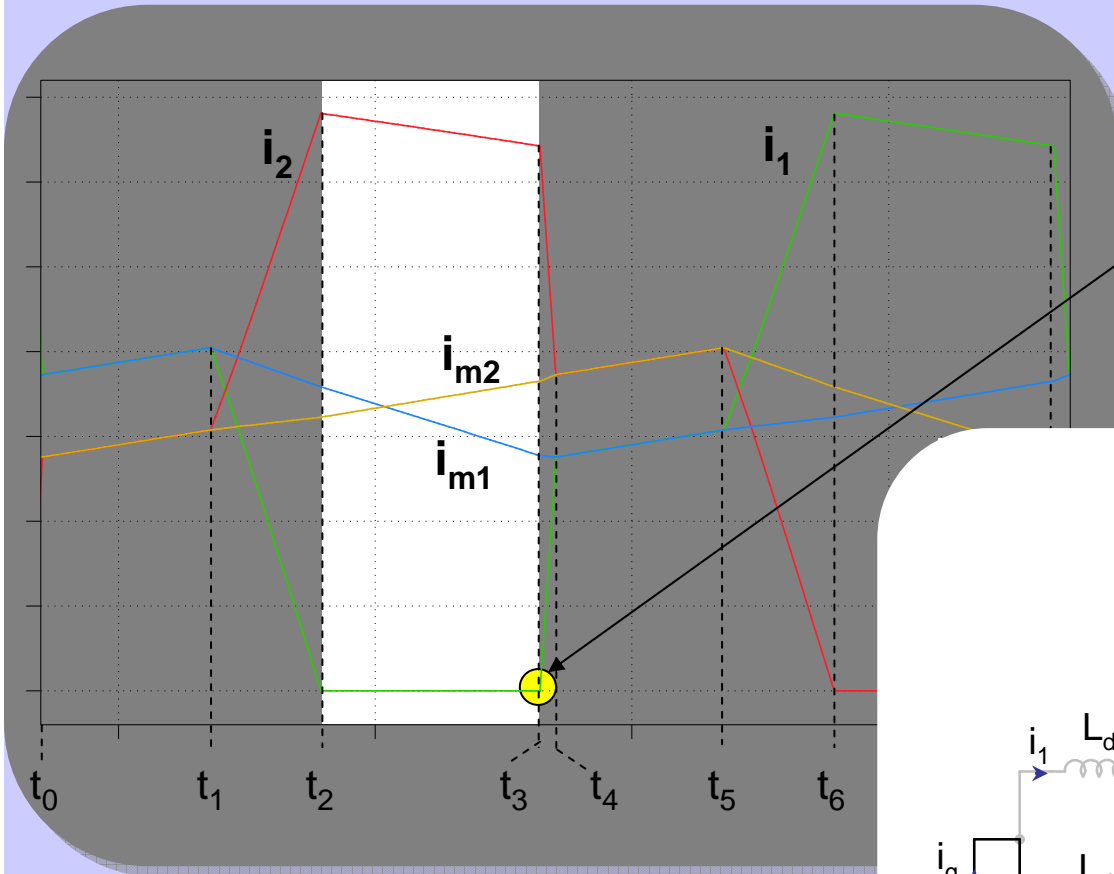
Operation for $d > d_{\min}$ (CCM)



$$T_{01} = t_1 - t_0$$

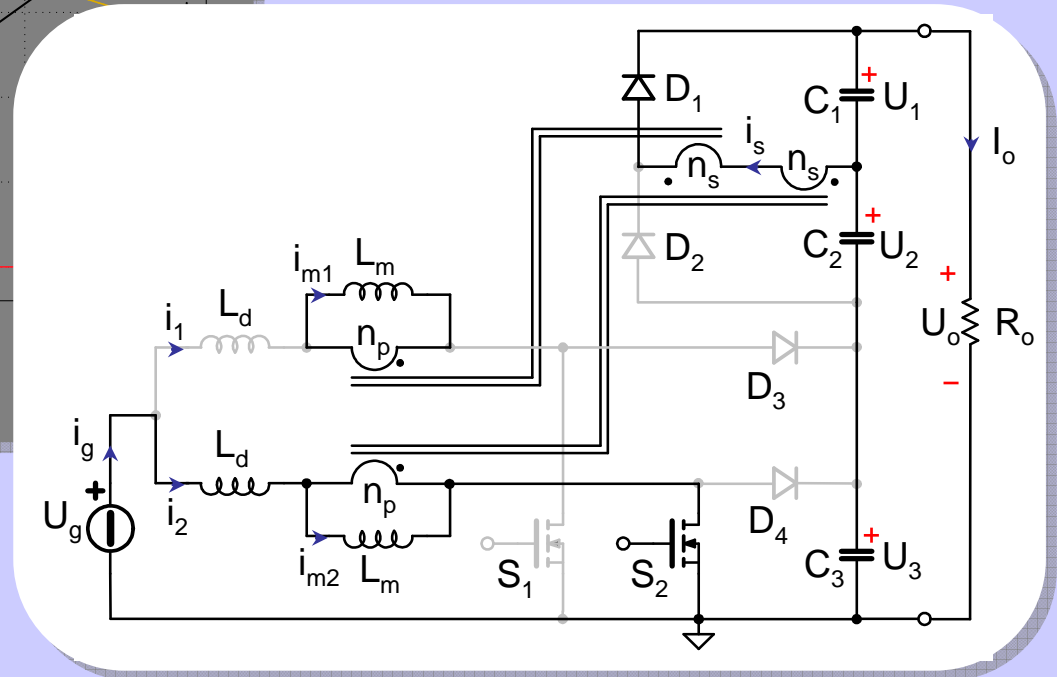


Operation for $d > d_{min}$ (CCM)

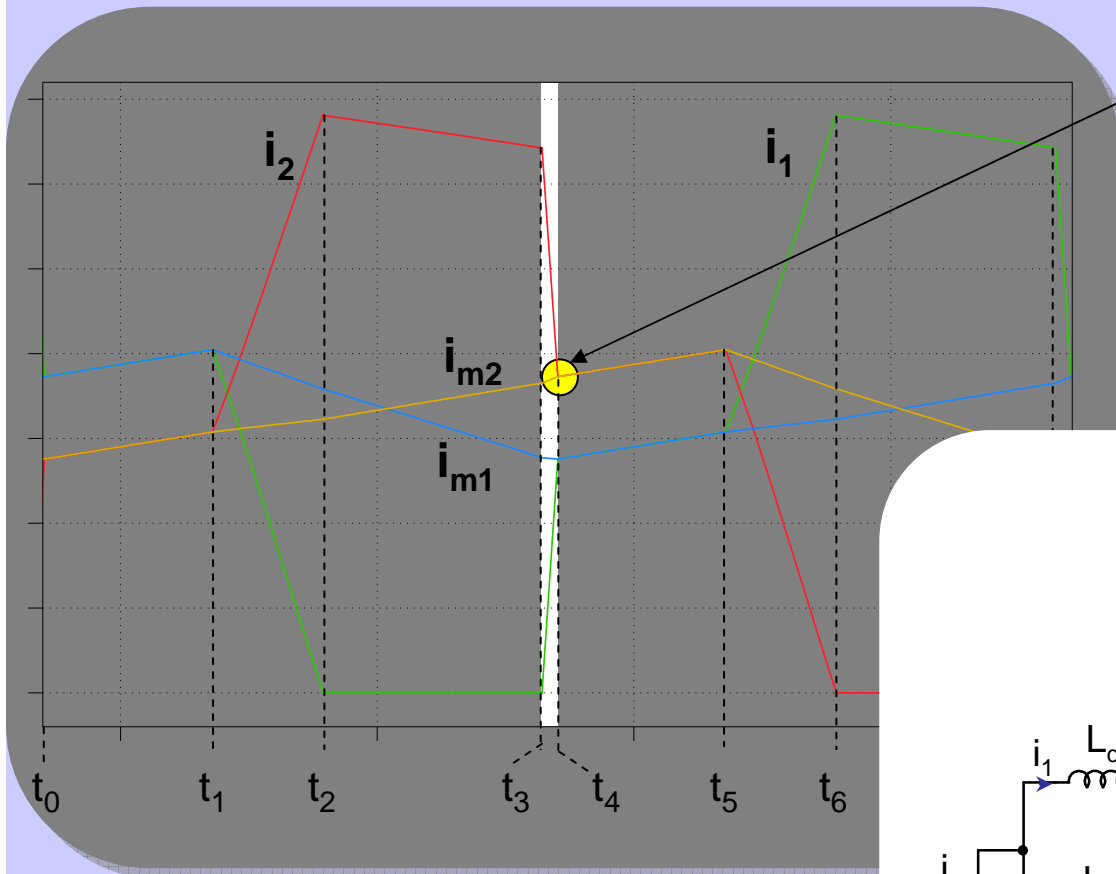


S_1 ZC turn on

$$T_{23} = t_3 - t_2$$

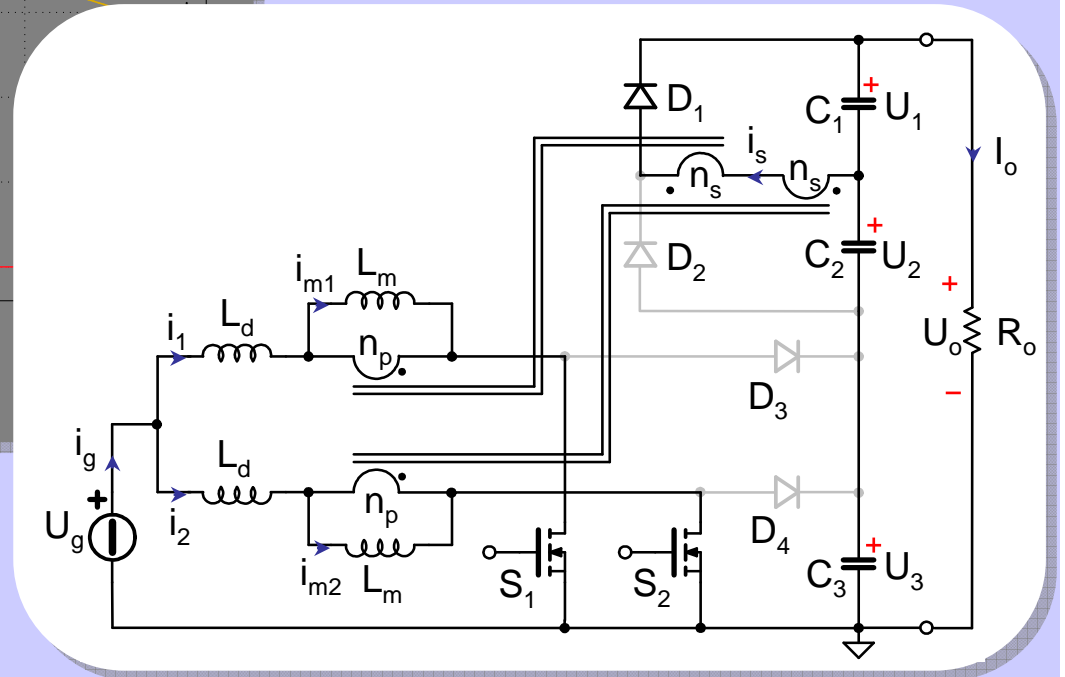


Operation for $d > d_{min}$ (CCM)

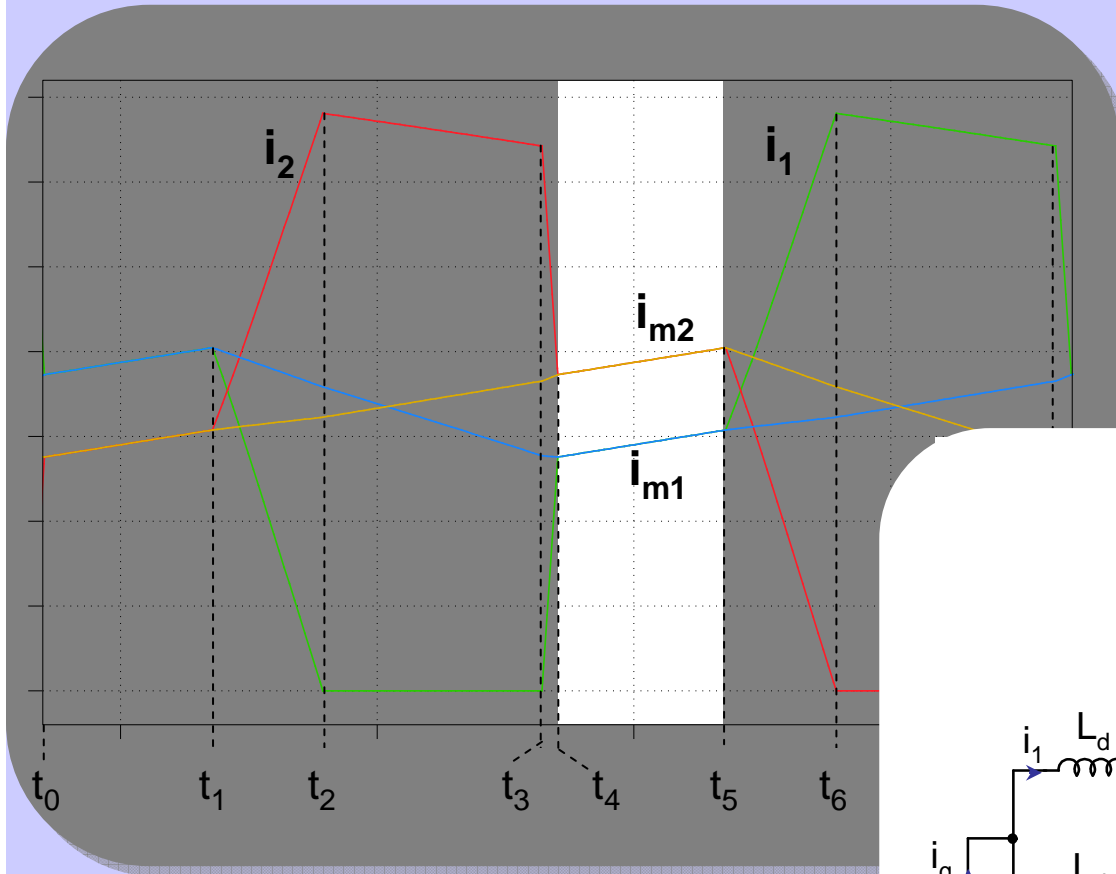


Soft D_1 turn off

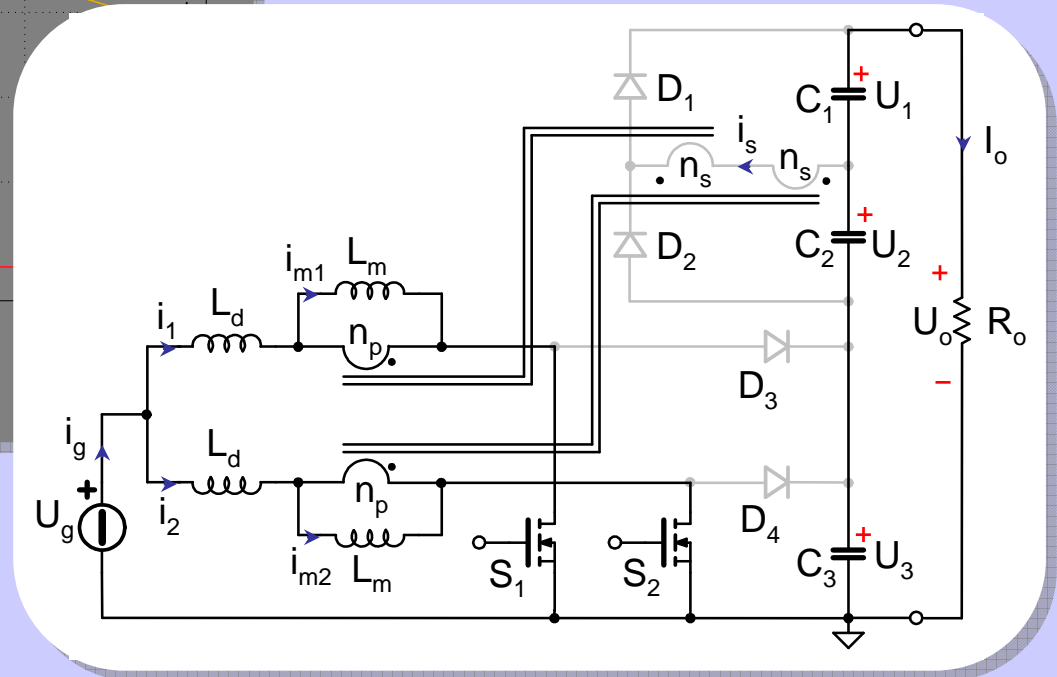
$$T_{34} = t_4 - t_3$$



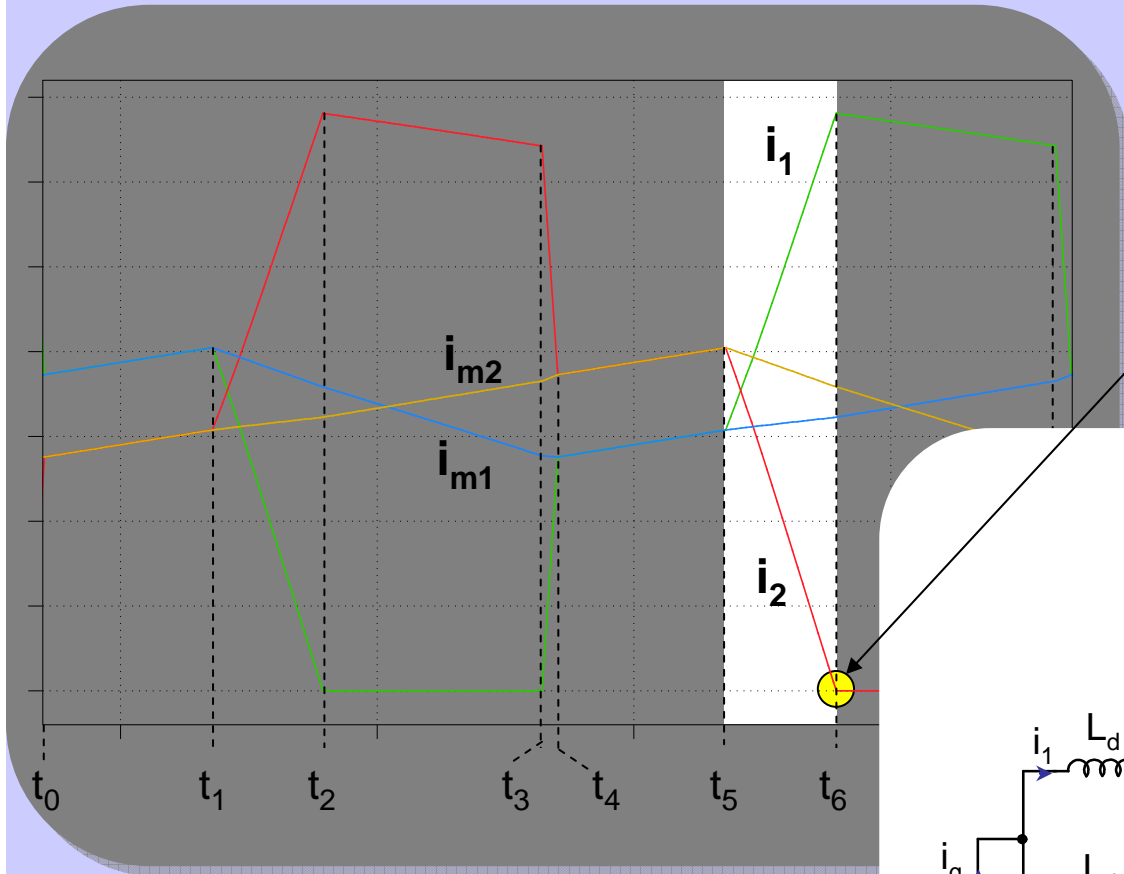
Operation for $d > d_{min}$ (CCM)



$$T_{45} = t_5 - t_4$$

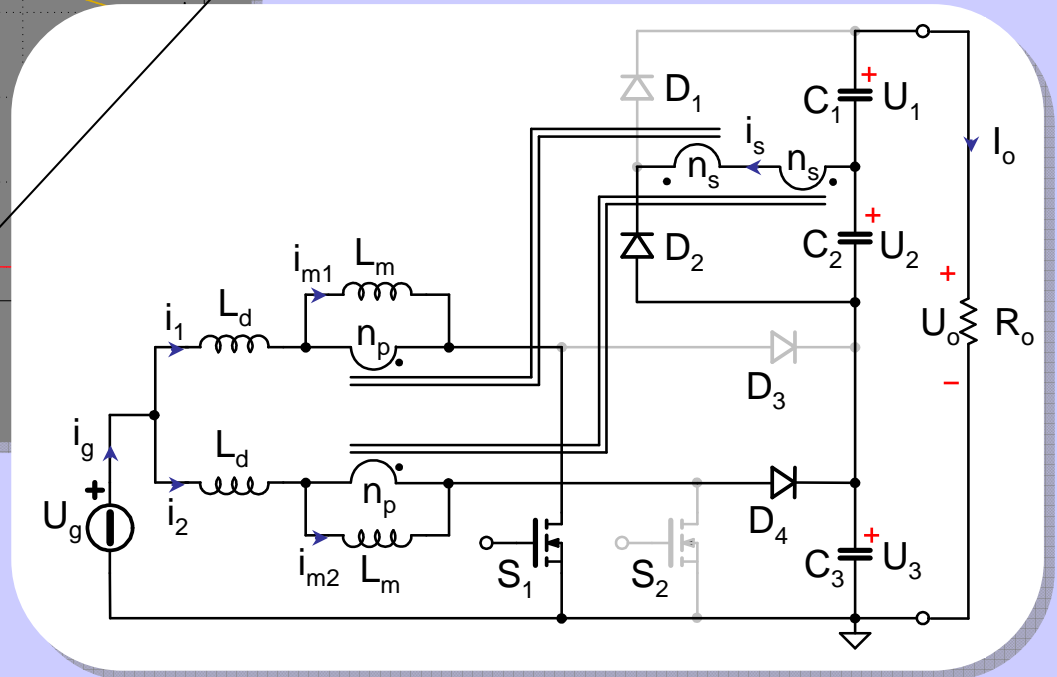


Operation for $d > d_{min}$ (CCM)

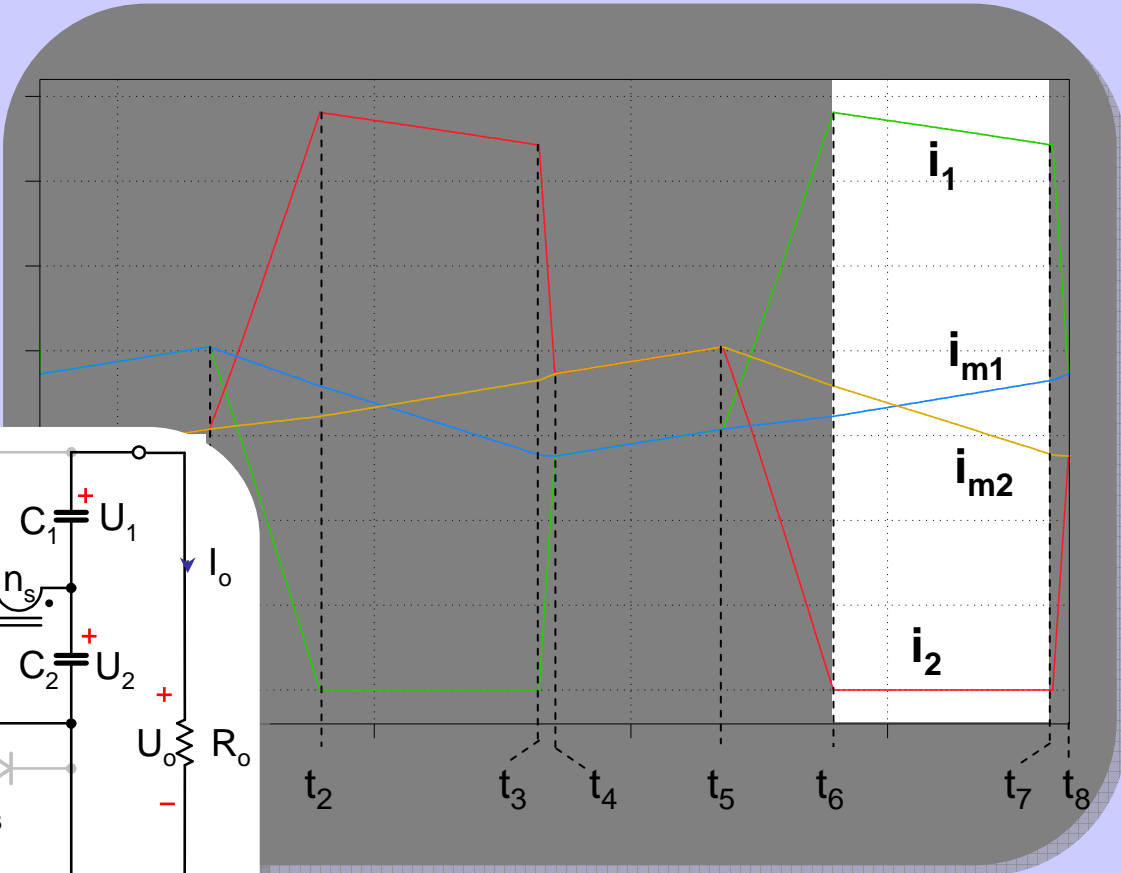
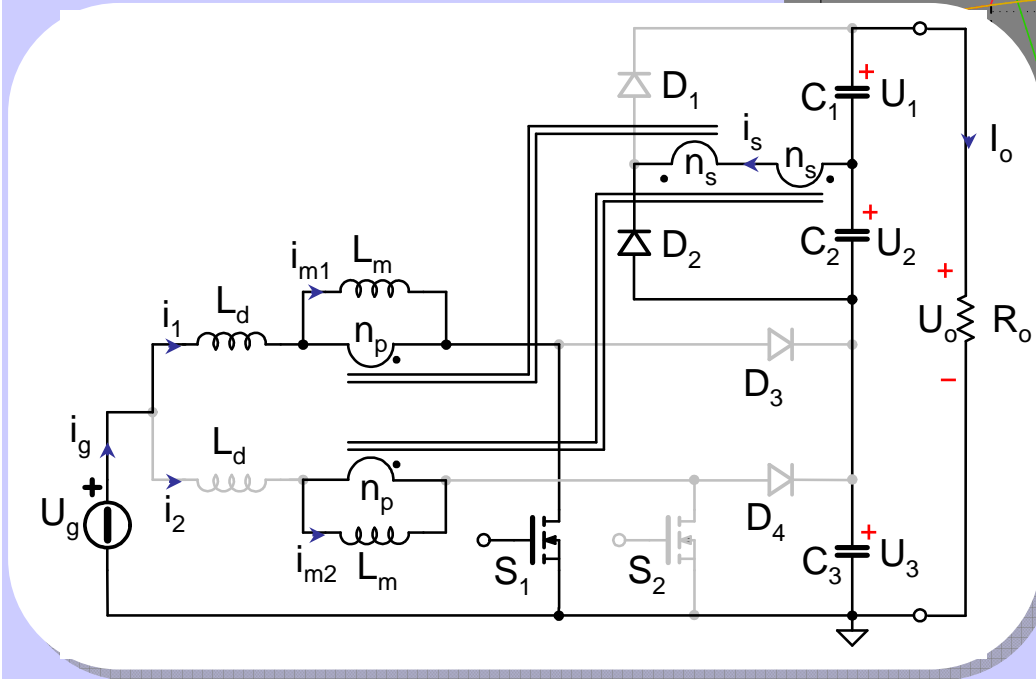


Soft D_4 turn off

$$T_{56} = t_6 - t_5$$



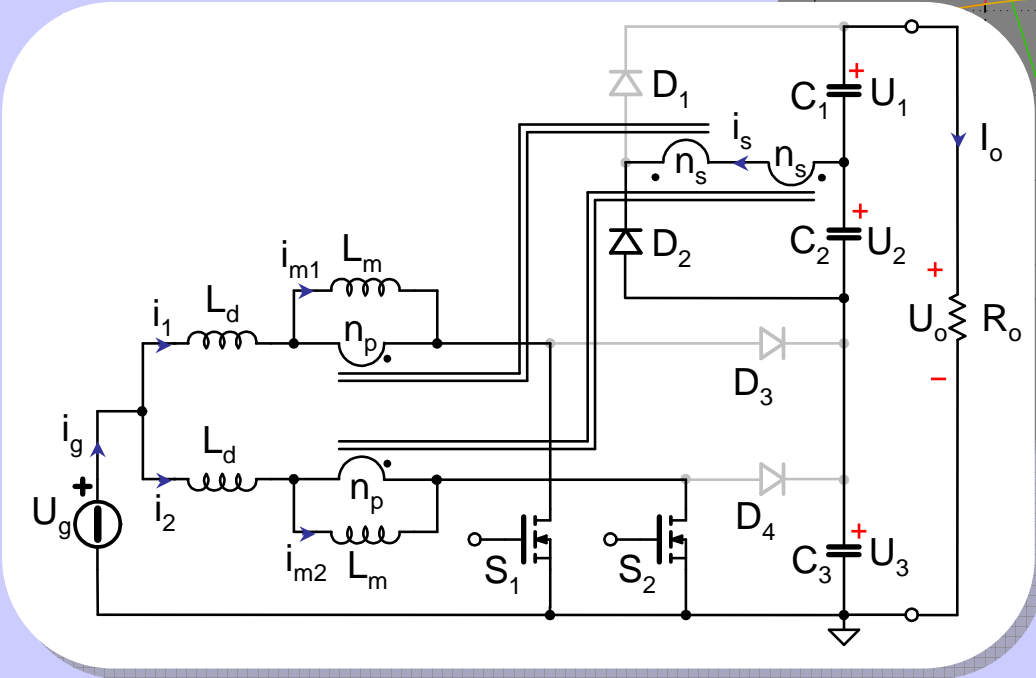
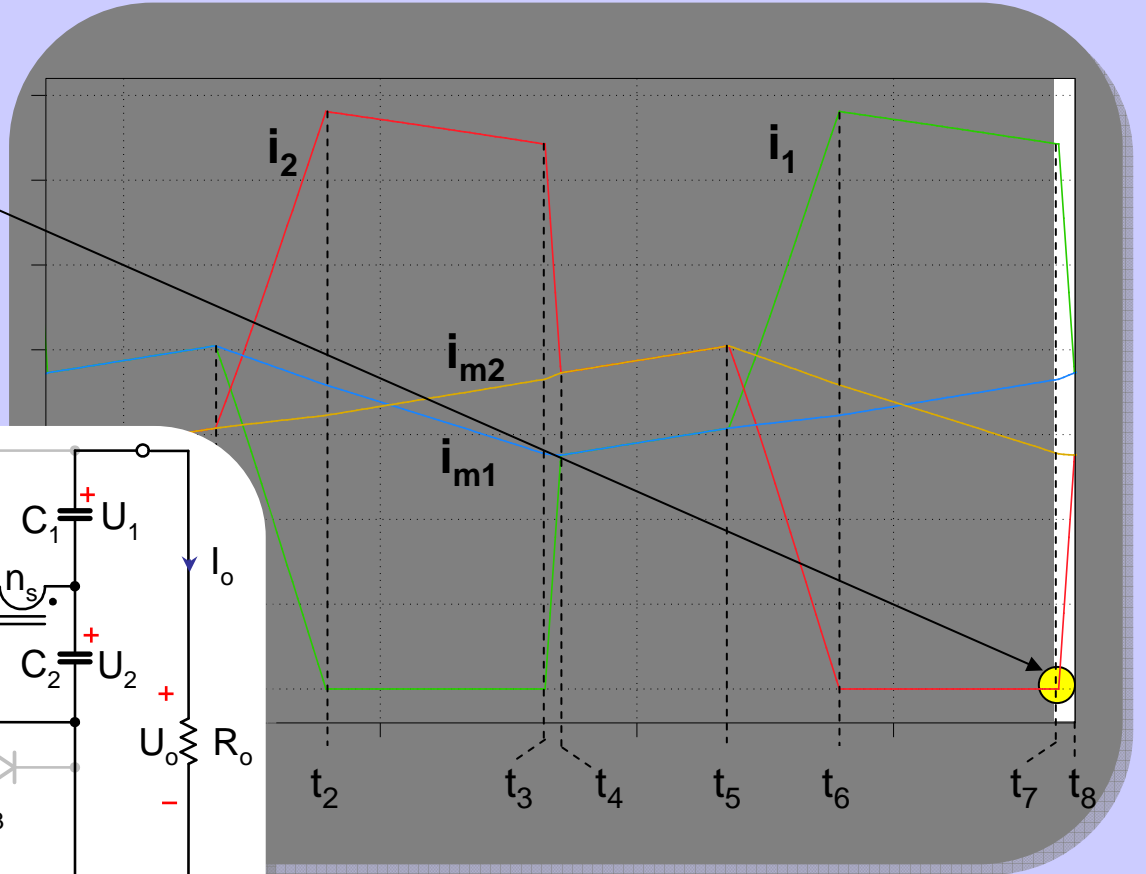
Operation for $d > d_{min}$ (CCM)



$$T_{67} = t_7 - t_6$$

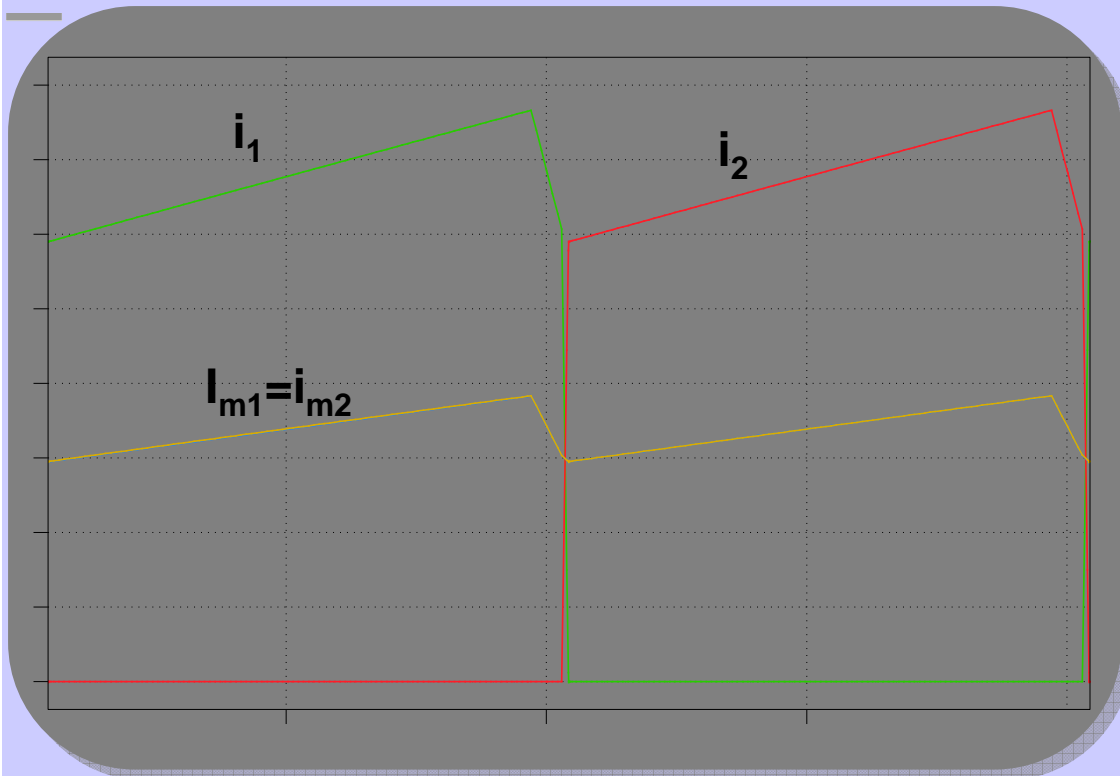
Operation for $d > d_{min}$ (CCM)

S_2 ZC turn on



$$T_{78} = t_8 - t_7$$

Operation for $d < d_{\min}$ (CCM)



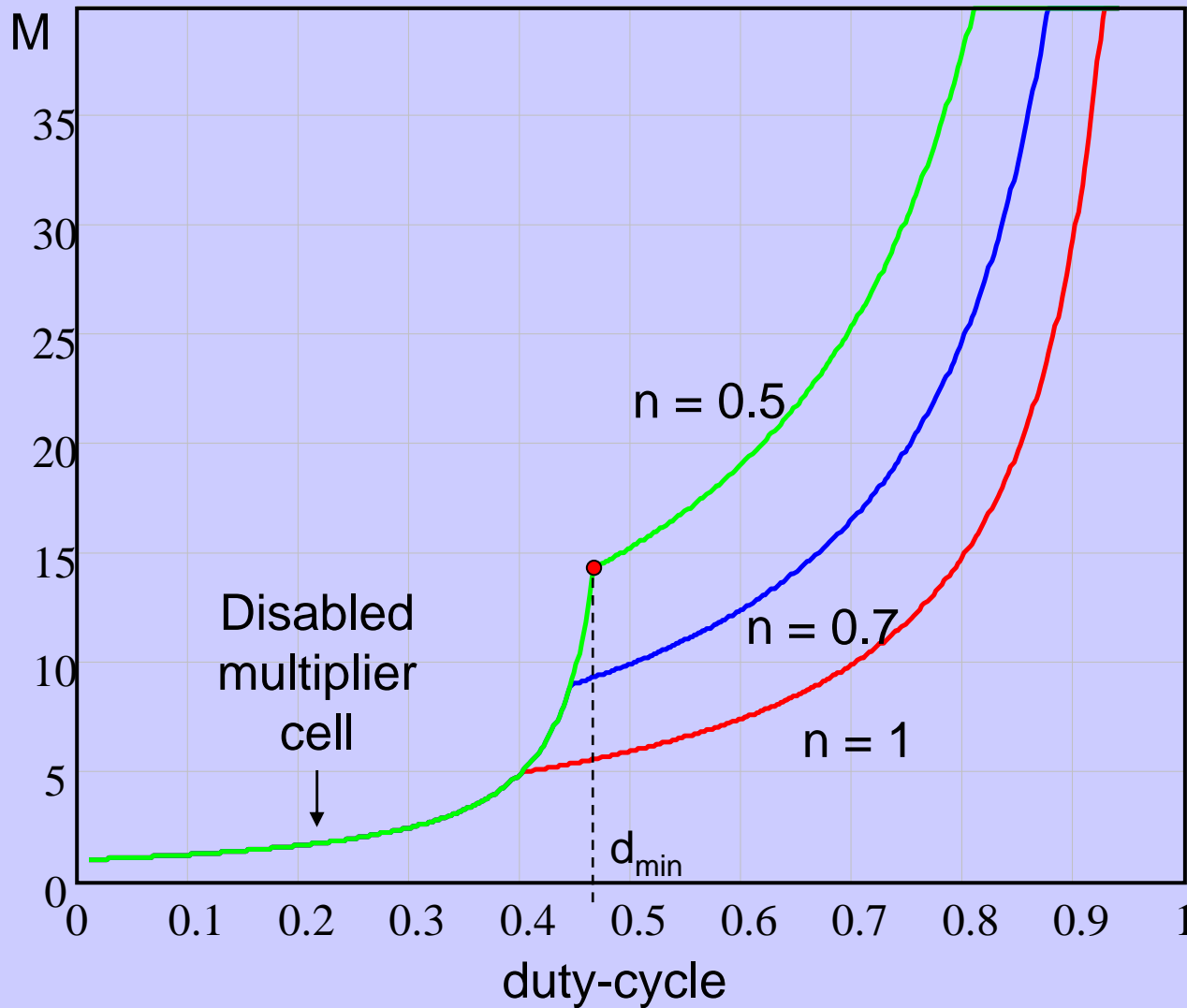
Voltage conversion ratio $d < d_{\min}$ (CCM):

$$M = \frac{U_o}{U_g} \approx \frac{1}{1-2d}$$

$$n = \frac{N_p}{N_s} \quad \frac{L_m}{L_m + L_d} \approx 1$$

- The multiplier cell is disabled ($u_1 = u_2 \approx 0, U_3 \approx U_o$)
- The switch voltage stress becomes equal to the output voltage
- The magnetizing currents are in phase

Voltage Conversion Ratio (CCM)



$$\frac{1}{1-2d_{min}} = \frac{n+2}{2} \frac{1}{1-d_{min}}$$



$$d_{min} = \frac{2}{n+4}$$

Minimum Switch Voltage Stress

Normalized switch voltage stress for $d = d_{\min}$:

$$U_{\text{sw1N}} = \frac{U_{\text{sw}}}{U_o} \approx \left(\frac{1}{1 - 2d_{\min}} \right) \frac{1}{M}$$
$$= \frac{n + 4}{nM}$$

Normalized switch voltage stress at nominal conditions ($d > d_{\min}$):

$$U_{\text{sw2N}} = \frac{U_{\text{sw}}}{U_o} \approx \frac{n}{2 + n}$$

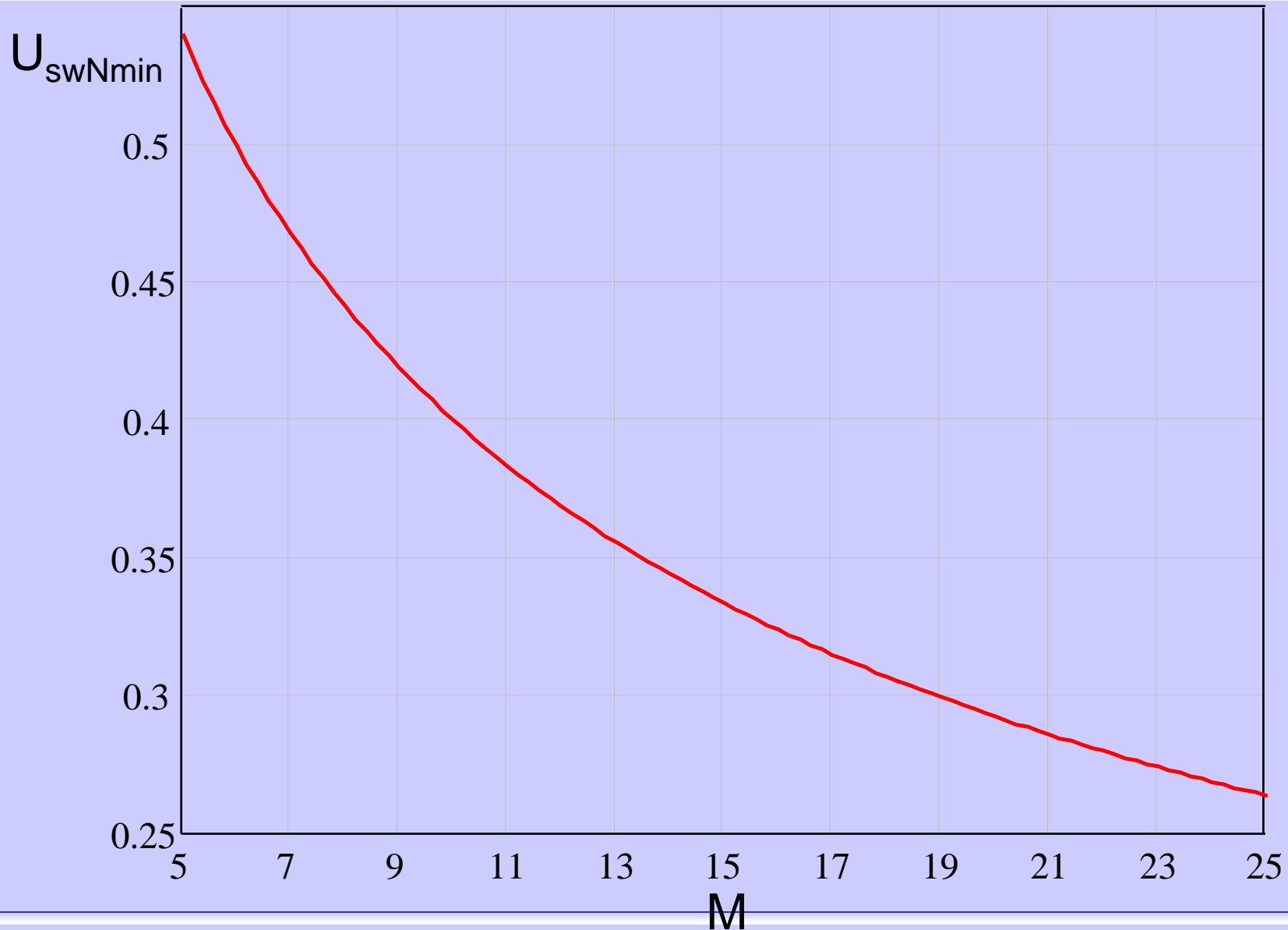
Optimum turns ratio:

$$U_{\text{sw1N}} = U_{\text{sw2N}}$$

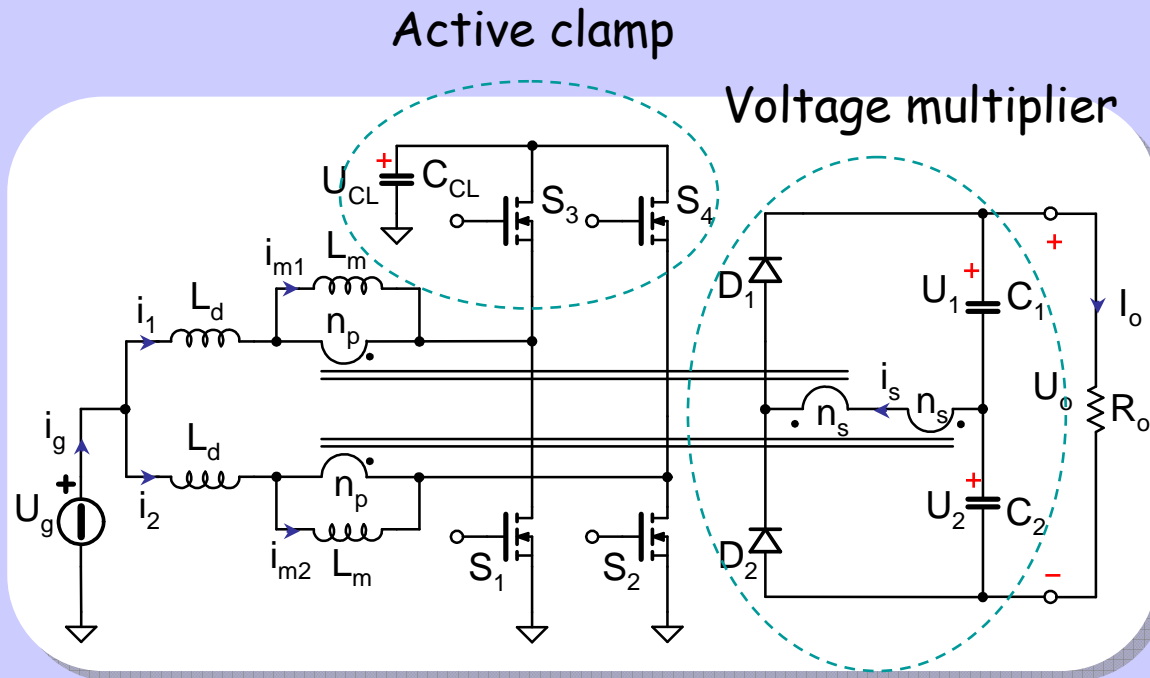


$$n_{\text{opt}} = \frac{3}{M-1} \left(1 + \sqrt{1 + \frac{8}{9}(M-1)} \right)$$

Minimum Switch Voltage Stress

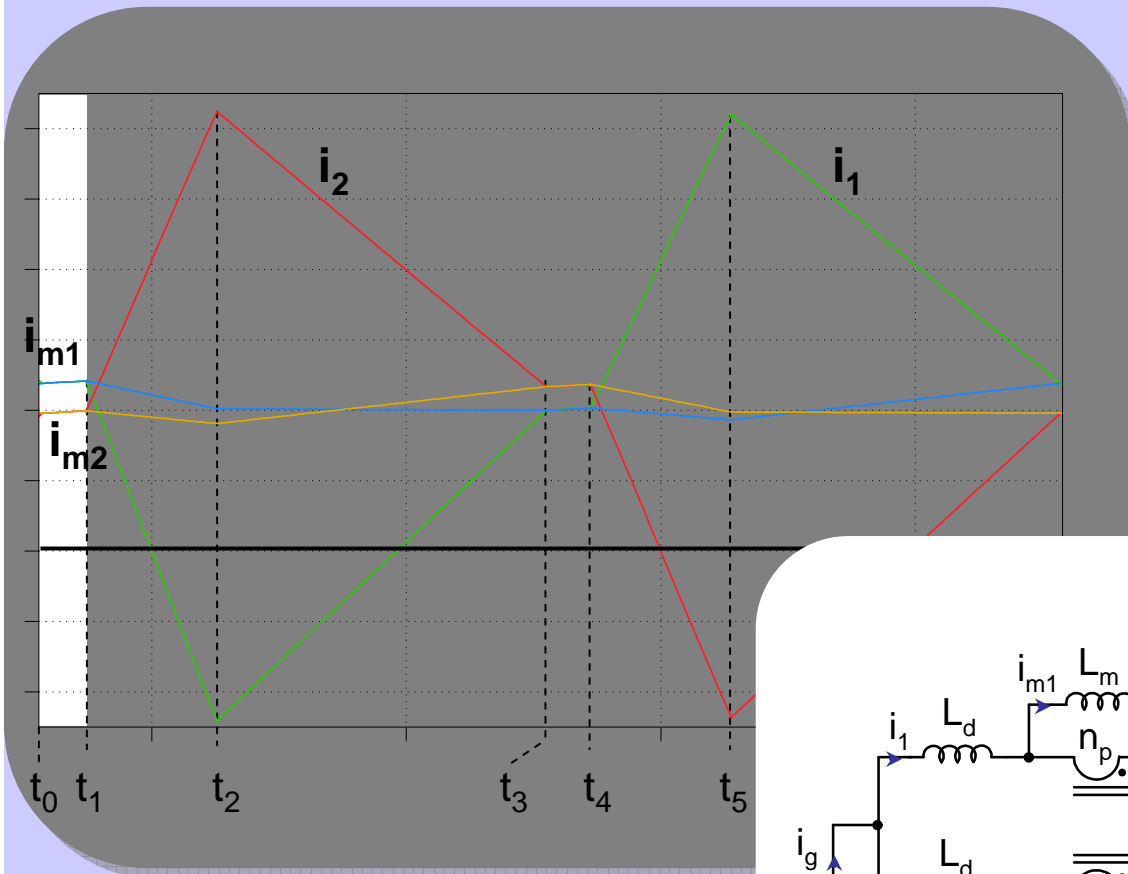


Isolated Interleaved High Gain Converter

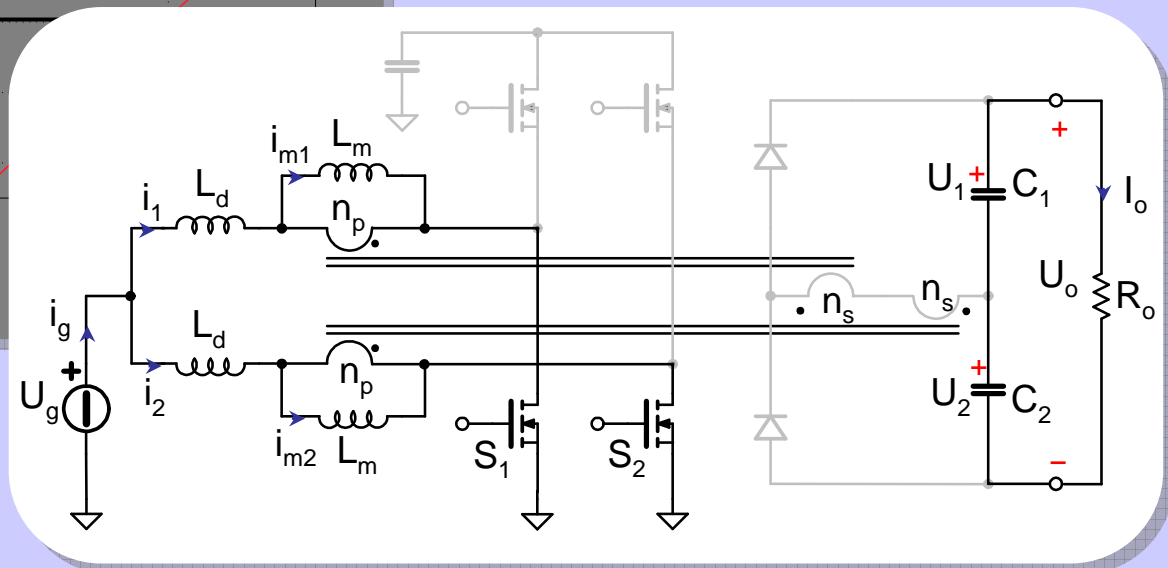


- ↑ Reduced switch and diode voltage stress
- ↑ Reduced input current ripple due to interleaved operation
- ↑ No reverse recovery losses (ZVS-ZCS switch turn on)
- ↑ Same operation mode independent of duty-cycle value
- ↓ High switch and winding current RMS value

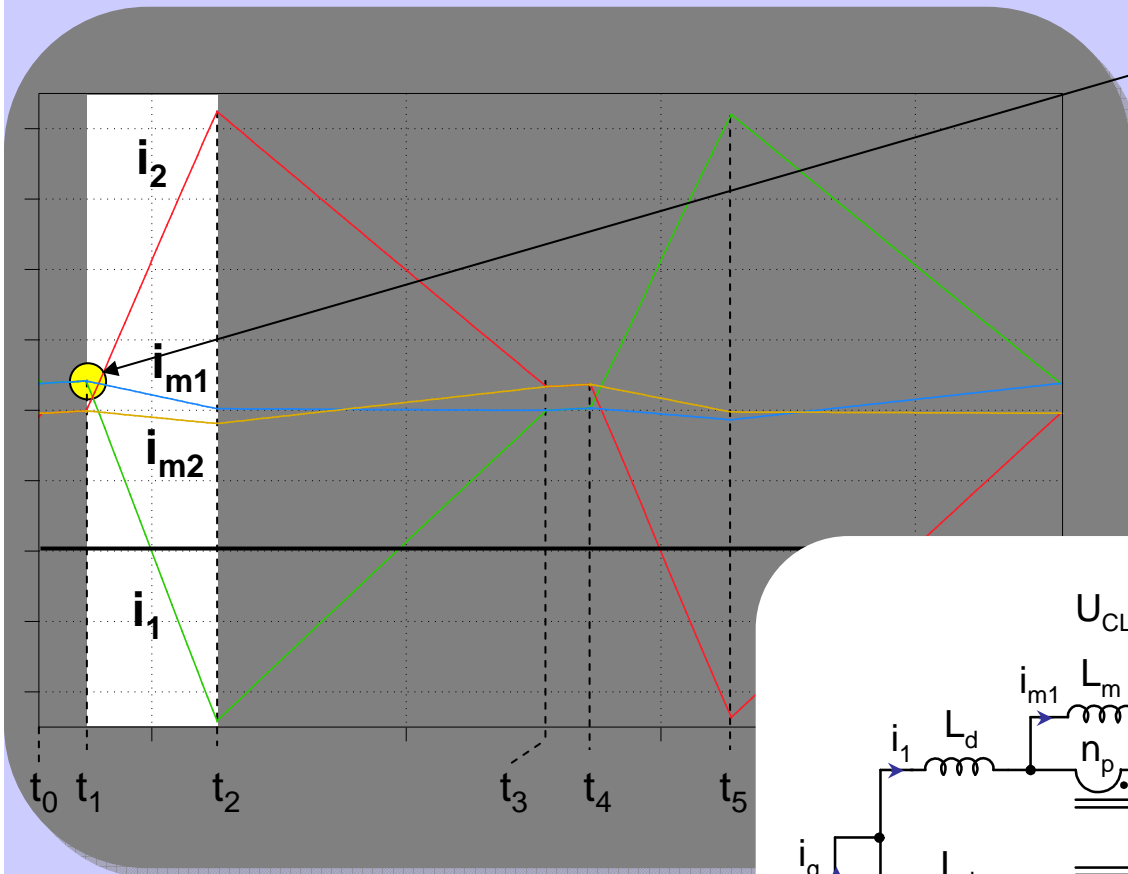
Main Waveforms



$$T_{01} = t_1 - t_0$$

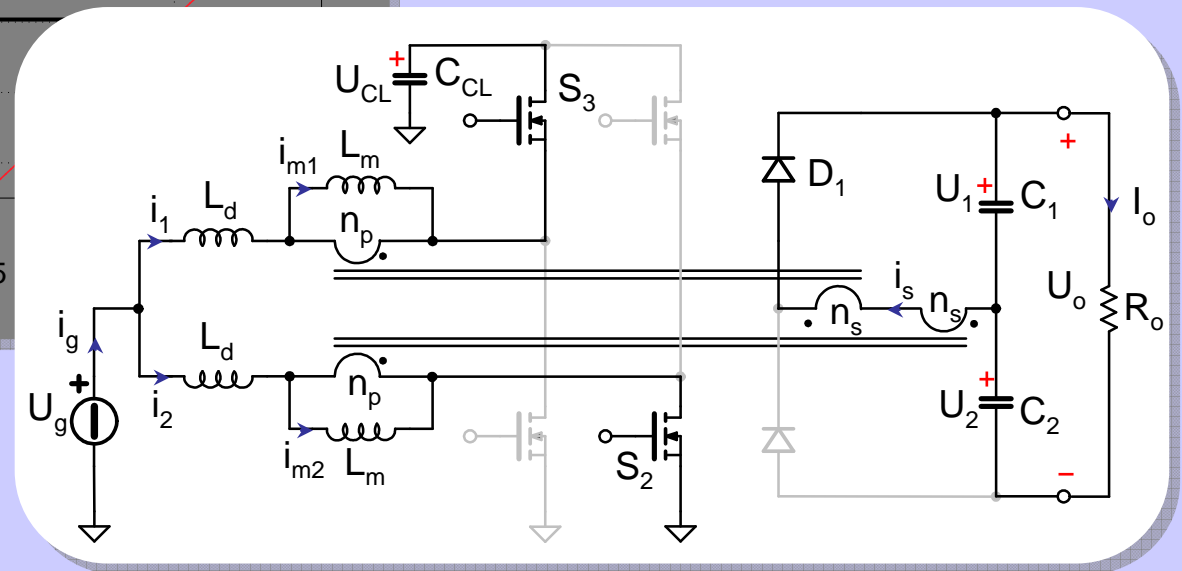


Main Waveforms

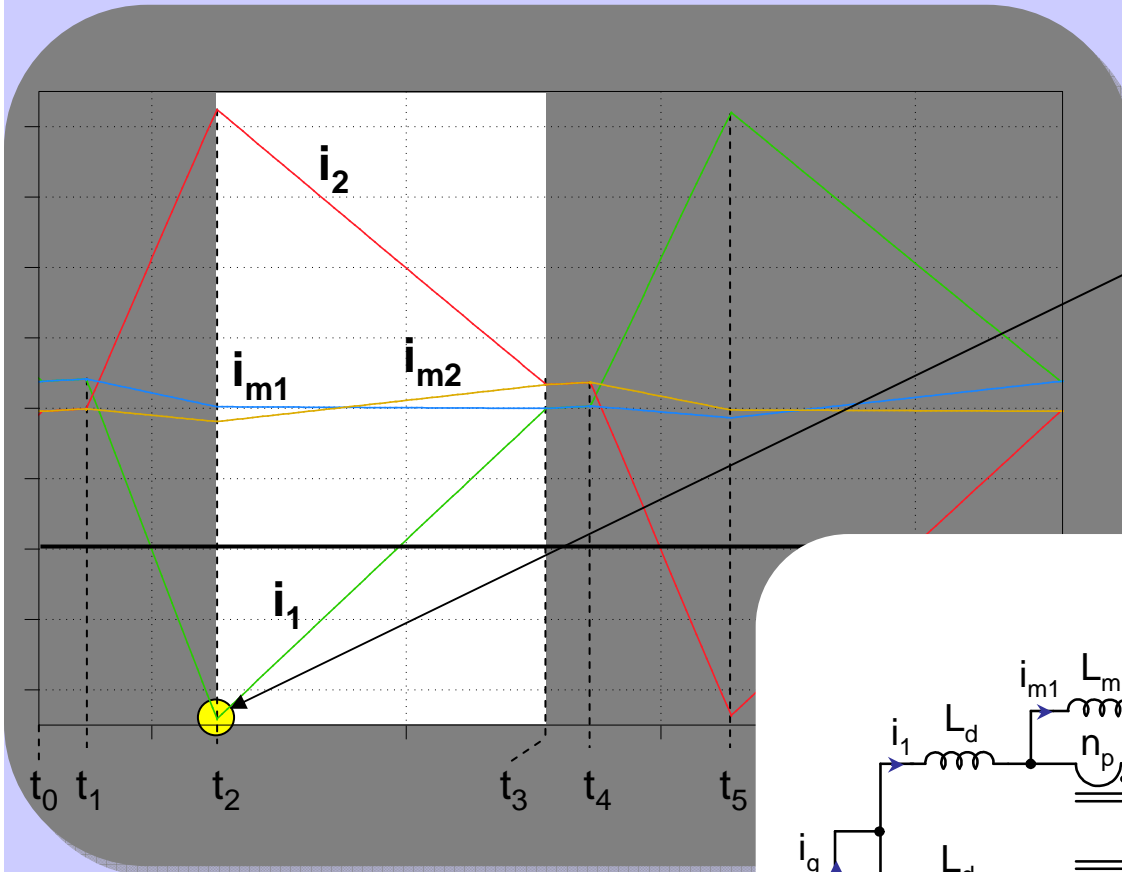


S_3 ZV & ZC turn on

$$T_{12} = t_2 - t_1$$

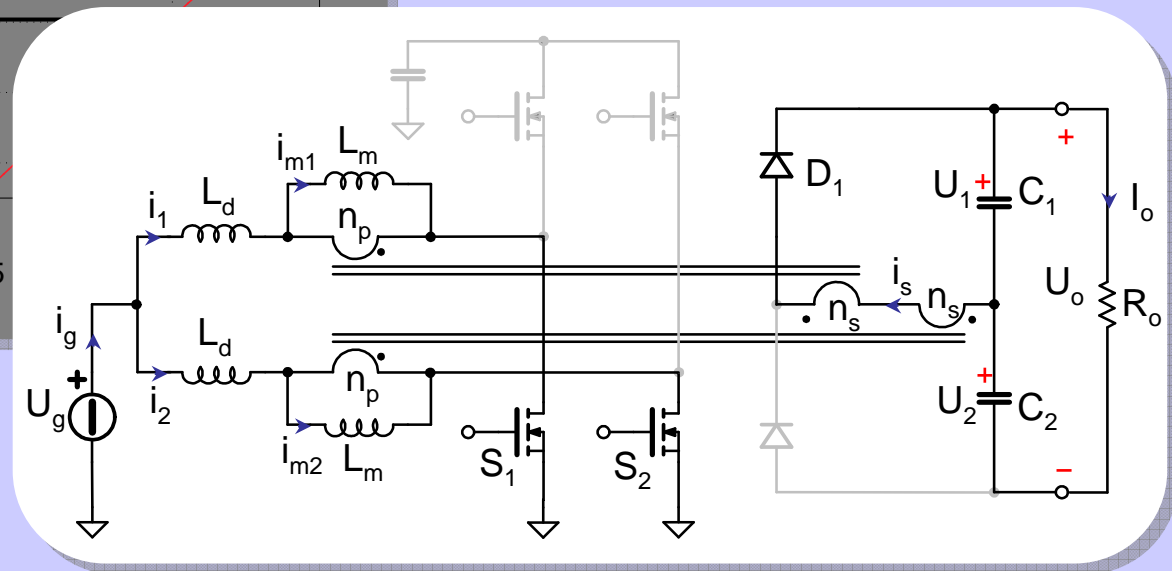


Main Waveforms

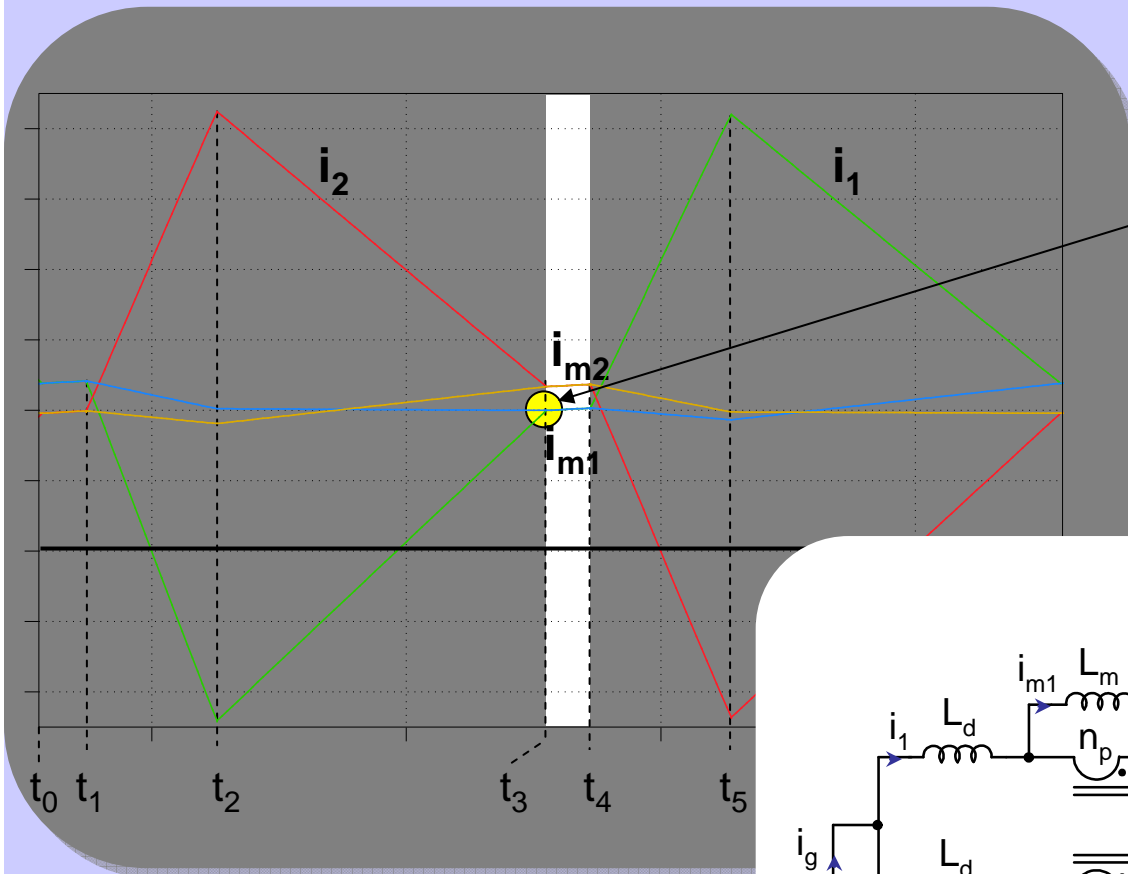


S_1 ZV & ZC turn on
(i_1 is negative when S_3
turns off)

$$T_{23} = t_3 - t_2$$

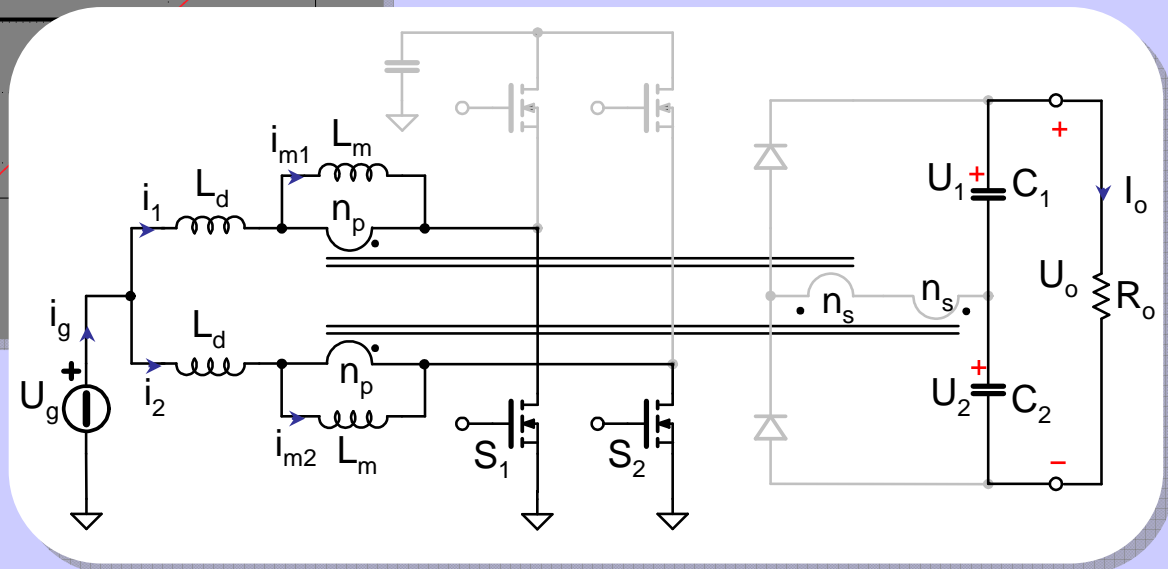


Main Waveforms



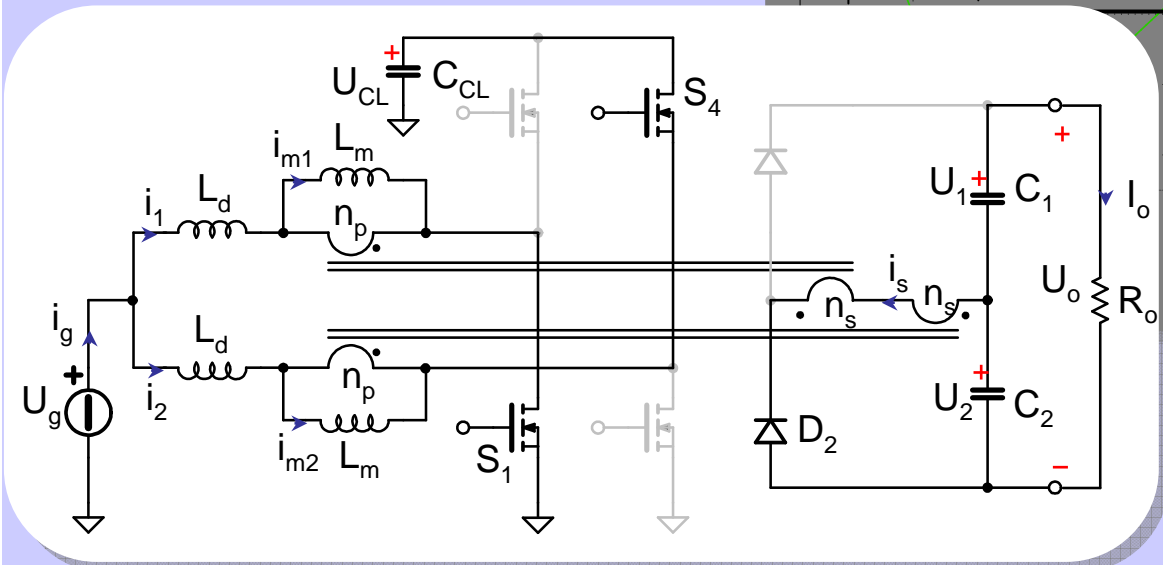
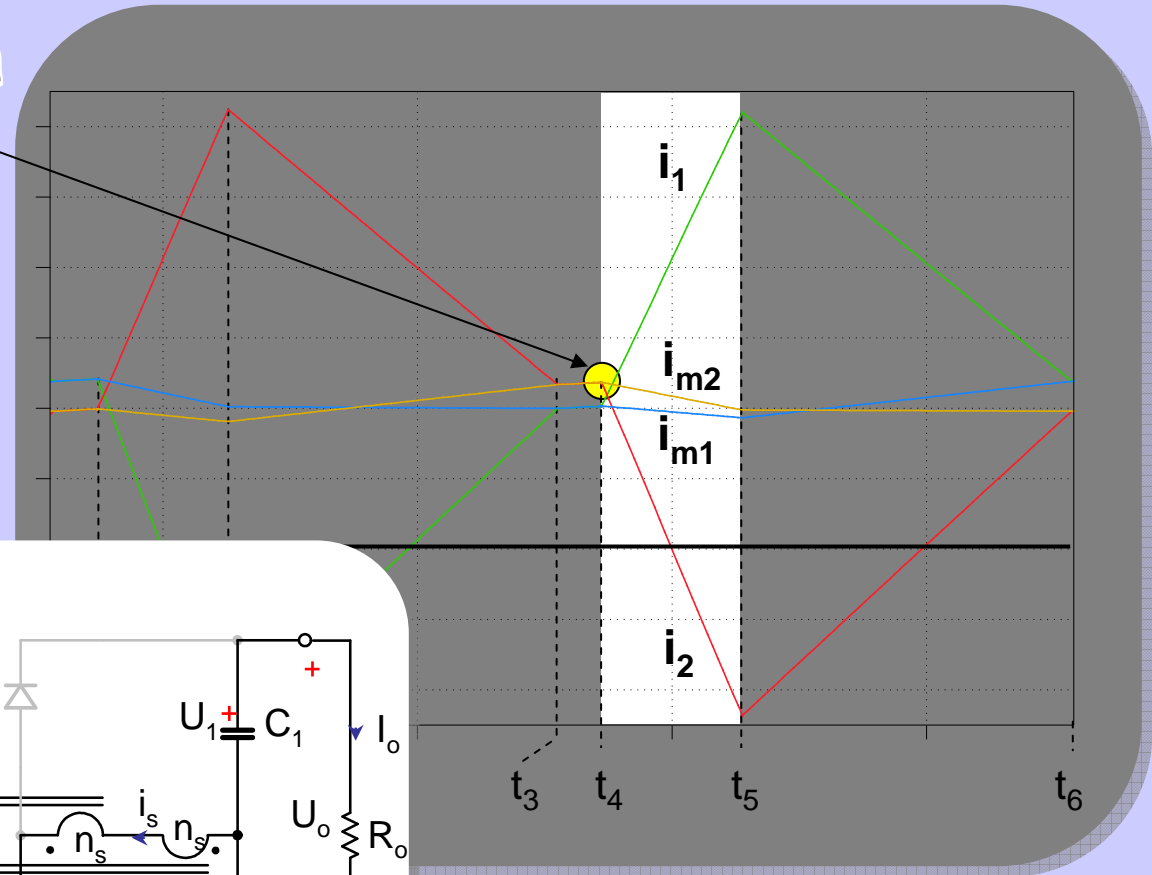
Soft D_1 turn off
(no reverse recovery problem)

$$T_{34} = t_4 - t_3$$



Main Waveforms

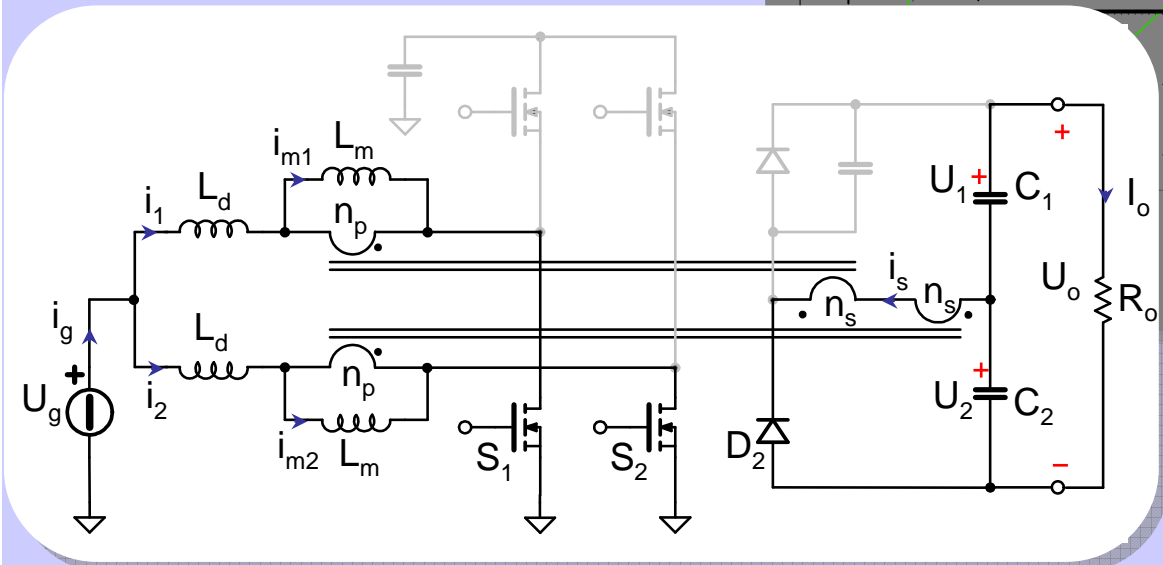
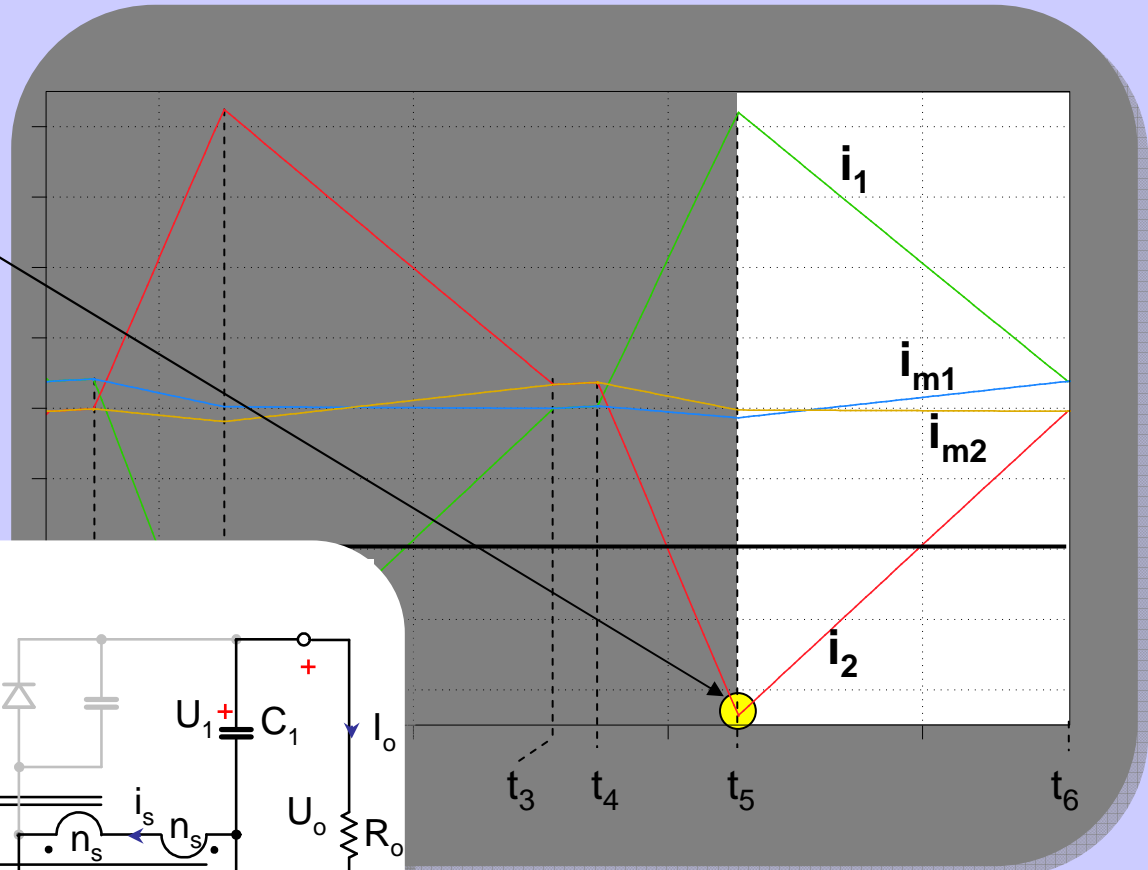
S_4 ZV & ZC turn on



$$T_{45} = t_5 - t_4$$

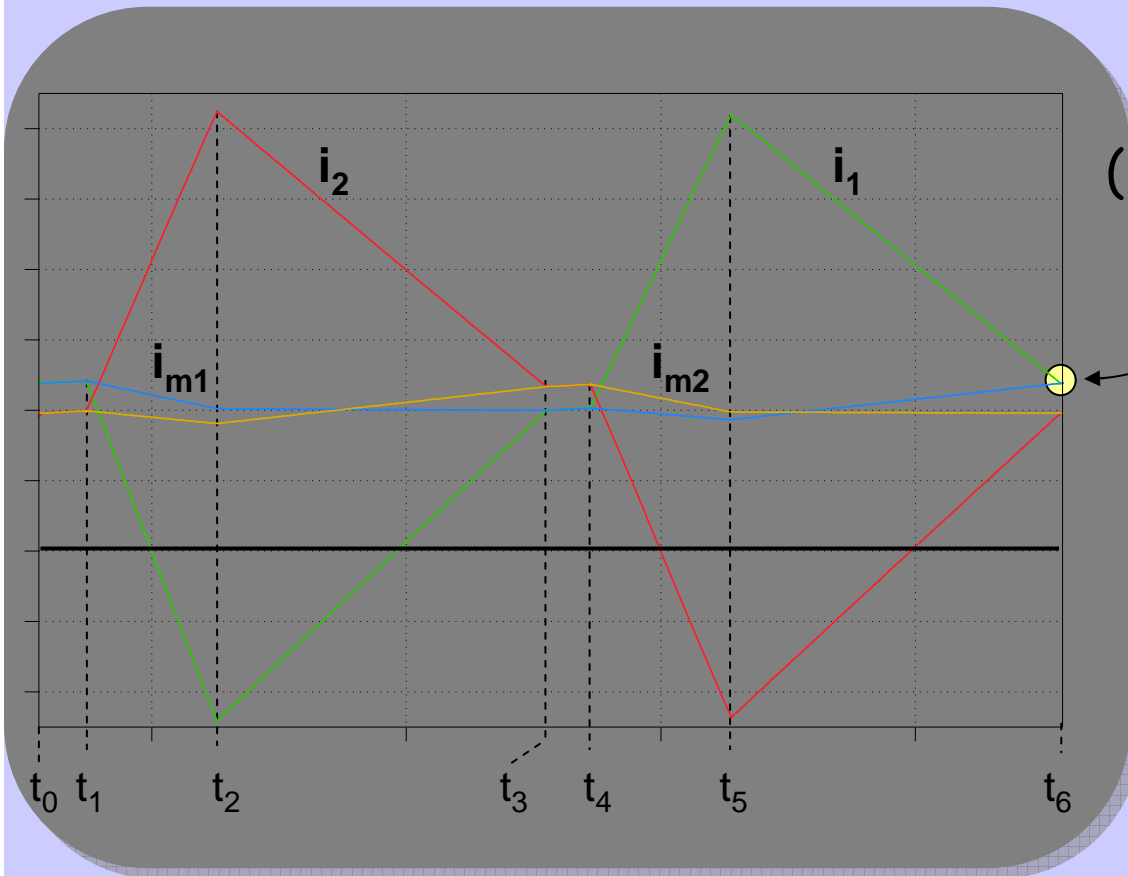
Main Waveforms

S_2 ZV & ZC turn on
(i_2 is negative when S_4
turns off)



$$T_{56} = t_6 - t_5$$

Main Waveforms

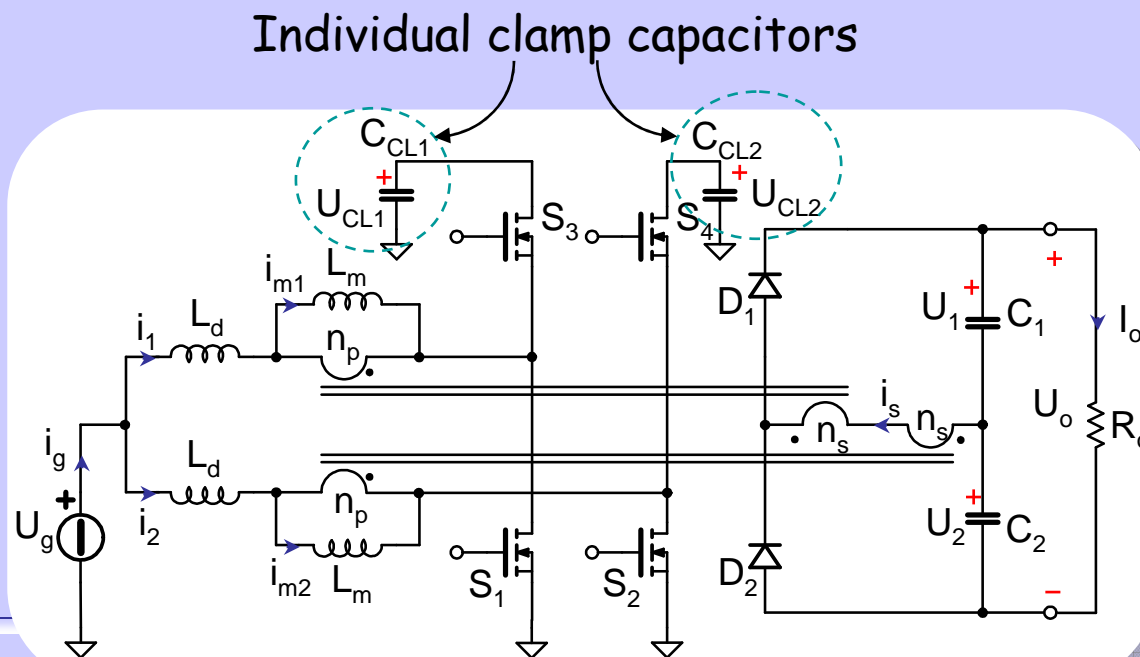


Soft D_2 turn off
(no reverse recovery problem)

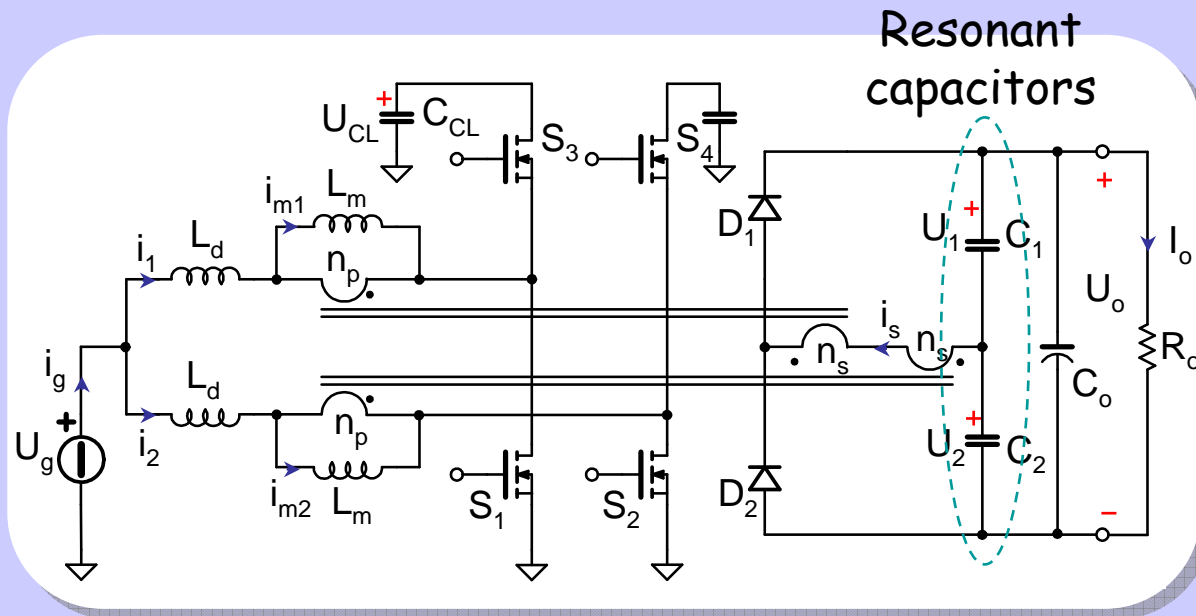
$$T_{01} = t_1 - t_2$$

Mismatch Sensitivity

- In case of parameter and/or duty-cycle mismatch between the interleaved boost sections severe current mismatch occurs.
- The solution is to employ individual clamp capacitors for each subsection (in this case, the mismatch is absorbed by a small difference between the clamp capacitor voltages)



Isolated Interleaved High Gain Resonant Converter



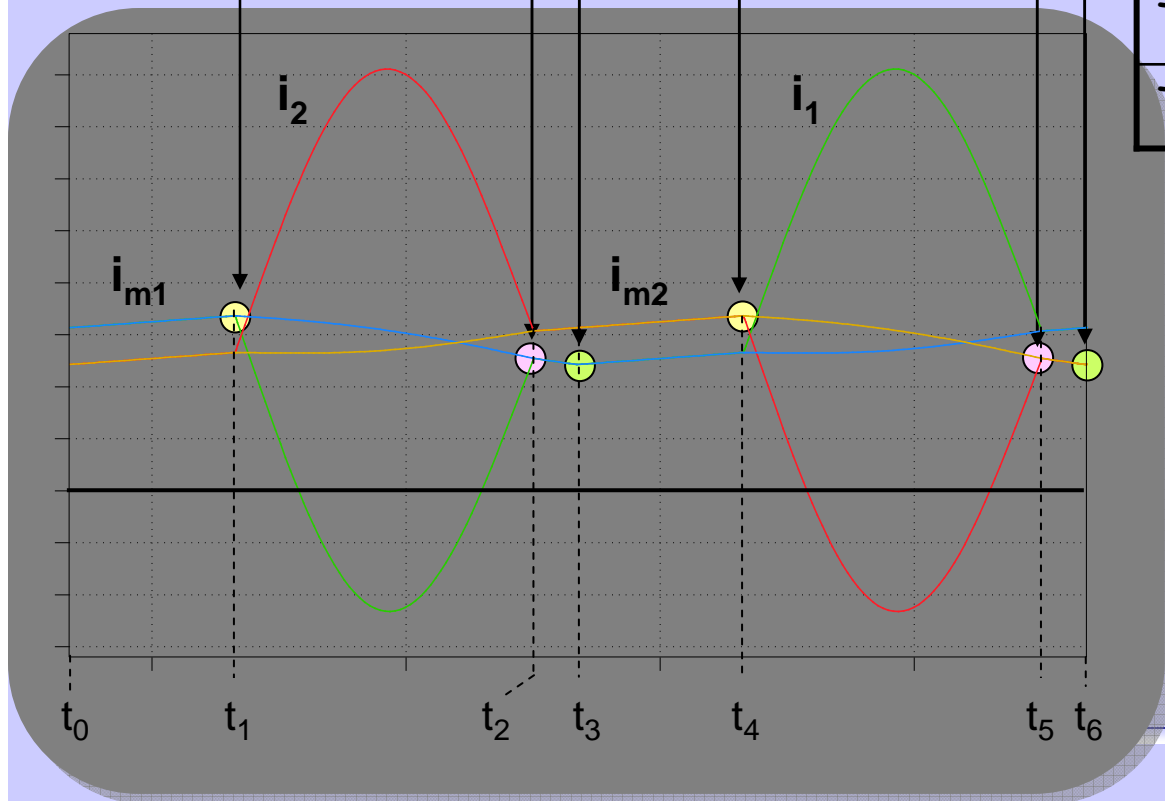
- ❑ Different operation mode is achieved by reducing the capacitor value of the voltage multiplier cell
- ❑ Half-cycle resonances occur between capacitor C_1 and C_2 and transformer leakage inductances L_d .

Main Waveforms

Hard S_1 and S_2 turn on

Soft D_1 and D_2 turn off

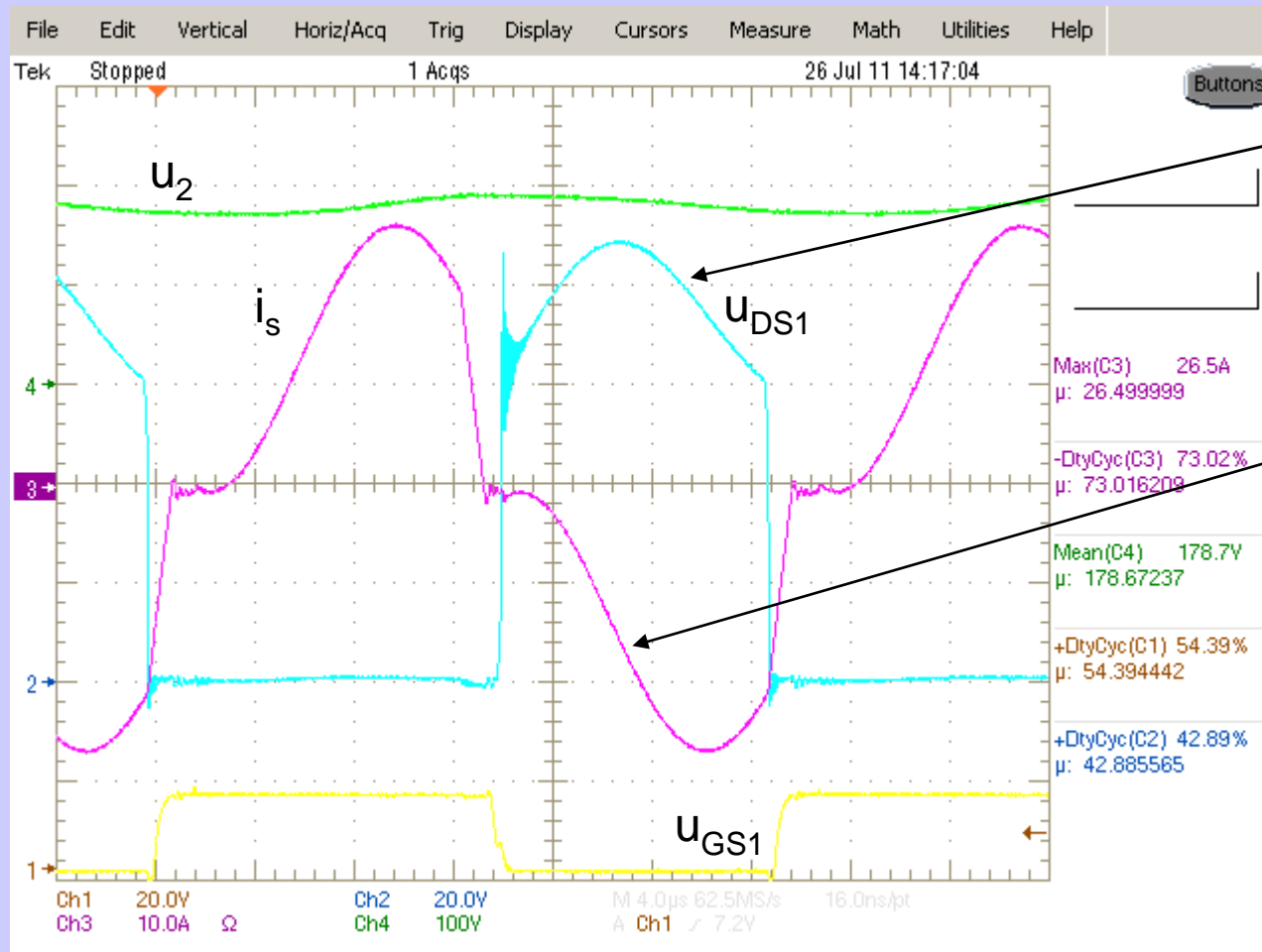
ZV & ZC turn on of S_3 and S_4



	S_1	S_2	D_1	D_2
$T_{01} = t_1 - t_0$	on	on	off	off
$T_{12} = t_2 - t_1$	off	on	on	off
$T_{23} = t_3 - t_2$	off	on	off	off
$T_{34} = t_4 - t_3$	on	on	off	off
$T_{45} = t_5 - t_4$	on	off	off	on
$T_{56} = t_6 - t_5$	on	off	off	off

Preliminary Experimental Results

$$U_g = 35V, U_o = 360V, P_o = 2500W, f_{sw} = 40kHz$$



High voltage ripple on clamp capacitors

Current waveform is half way between non resonant and resonant behaviors



Conclusions

- For high power applications, high step-up converters working with a quite high input current value should have a continuous input current absorption.
- Interleaved operation at input side helps to reduce the input current ripple as well as to share the total input current between different conversion subsections.
- A voltage multiplier at the output side avoids the use of dissipative snubbers across the output diodes.
- Isolated structures operate in the same manner independent of the duty-cycle value (they are better than the non-isolated ones)